



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

MAX19996A

General Description

The MAX19996A single, high-linearity downconversion mixer provides 8.7dB conversion gain, +24.5dBm IIP3, and 9.8dB noise figure for 2000MHz to 3900MHz WCS, LTE, WiMAX™, and MMDS wireless infrastructure applications. With an ultra-wide LO frequency range of 2100MHz to 4000MHz, the MAX19996A can be used in either low-side or high-side LO injection architectures for virtually all 2.5GHz and 3.5GHz applications. For a 2.5GHz variant tuned specifically for low-side injection, refer to the MAX19996 data sheet.

In addition to offering excellent linearity and noise performance, the MAX19996A also yields a high level of component integration. This device includes a double-balanced passive mixer core, an IF amplifier, and an LO buffer. On-chip baluns are also integrated to allow for single-ended RF and LO inputs. The MAX19996A requires a nominal LO drive of 0dBm, and supply current is typically 230mA at VCC = 5.0V, or 150mA at VCC = 3.3V.

The MAX19996A is pin compatible with the MAX19996 2000MHz to 3000MHz mixer. The device is also pin similar with the MAX9984/MAX9986/MAX9986A 400MHz to 1000MHz mixers and the MAX9993/MAX9994/MAX9996 1700MHz to 2200MHz mixers, making this entire family of downconverters ideal for applications where a common PCB layout is used for multiple frequency bands.

The MAX19996A is available in a compact 5mm x 5mm, 20-pin thin QFN with an exposed pad. Electrical performance is guaranteed over the extended -40°C to +85°C temperature range.

Applications

2.3GHz WCS Base Stations
2.5GHz WiMAX and LTE Base Stations
2.7GHz MMDS Base Stations
3.5GHz WiMAX and LTE Base Stations
Fixed Broadband Wireless Access
Wireless Local Loop
Private Mobile Radios
Military Systems

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Features

- ◆ 2000MHz to 3900MHz RF Frequency Range
- ◆ 2100MHz to 4000MHz LO Frequency Range
- ◆ 50MHz to 500MHz IF Frequency Range
- ◆ 8.7dB Conversion Gain
- ◆ 9.8dB Noise Figure
- ◆ +24.5dBm Typical Input IP3
- ◆ 11dBm Typical Input 1dB Compression Point
- ◆ 67dBc Typical 2LO-2RF Spurious Rejection at PRF = -10dBm
- ◆ Integrated LO Buffer
- ◆ Integrated RF and LO Baluns for Single-Ended Inputs
- ◆ Low -3dBm to +3dBm LO Drive
- ◆ Pin Compatible with the MAX19996 2000MHz to 3000MHz Mixer
- ◆ Pin Similar with the MAX9993/MAX9994/MAX9996 Series of 1700MHz to 2200MHz Mixers and the MAX9984/MAX9986/MAX9986A Series of 400MHz to 1000MHz Mixers
- ◆ Single 5.0V or 3.3V Supply
- ◆ External Current-Setting Resistors Provide Option for Operating Device in Reduced-Power/Reduced-Performance Mode

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX19996AETP+	-40°C to +85°C	20 Thin QFN-EP*
MAX19996AETP+T	-40°C to +85°C	20 Thin QFN-EP*

+ Denotes a lead(Pb)-free/RoHS-compliant package.

*EP = Exposed pad.

T = Tape and reel.



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For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

Pin Configuration/Functional Diagram appears at end of data sheet.

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ABSOLUTE MAXIMUM RATINGS

V_{CC} to GND-0.3V to +5.5V
 IF+, IF-, LO to GND-0.3V to (V_{CC} + 0.3V)
 RF, LO Input Power+12dBm
 RF, LO Current (RF and LO is DC shorted to GND
 through a balun).....50mA
 Continuous Power Dissipation (Note 1)5.0W
 θ_{JA} (Notes 2, 3).....+38°C/W

θ_{JC} (Notes 1, 3).....13°C/W
 Operating Case Temperature
 Range (Note 4).....T_C = -40°C to +85°C
 Junction Temperature+150°C
 Storage Temperature Range-65°C to +150°C
 Lead Temperature (soldering, 10s)+300°C

Note 1: Based on junction temperature $T_J = T_C + (\theta_{JC} \times V_{CC} \times I_{CC})$. This formula can be used when the temperature of the exposed pad is known while the device is soldered down to a PCB. See the *Applications Information* section for details. The junction temperature must not exceed +150°C.

Note 2: Junction temperature $T_J = T_A + (\theta_{JA} \times V_{CC} \times I_{CC})$. This formula can be used when the ambient temperature of the PCB is known. The junction temperature must not exceed +150°C.

Note 3: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maxim-ic.com/thermal-tutorial.

Note 4: T_C is the temperature on the exposed pad of the package. T_A is the ambient temperature of the device and PCB.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

5.0V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, V_{CC} = 4.75V to 5.25V, no input AC signals. T_C = -40°C to +85°C, unless otherwise noted. Typical values are at V_{CC} = 5.0V, T_C = +25°C, all parameters are production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V _{CC}		4.75	5.0	5.25	V
Supply Current	I _{CC}			230	245	mA

3.3V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, V_{CC} = 3.0V to 3.6V, no input AC signals. T_C = -40°C to +85°C, unless otherwise noted. Typical values are at V_{CC} = 3.3V, T_C = +25°C, parameters are guaranteed by design and not production tested, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V _{CC}		3.0	3.3	3.6	V
Supply Current	I _{CC}	Total supply current, V _{CC} = 3.3V		150		mA

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RECOMMENDED AC OPERATING CONDITIONS

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
RF Frequency Range	f_{RF}	Typical Application Circuit with $C1 = 8.2\text{pF}$, see Table 1 for details (Note 5)	2000		3000	MHz
		Typical Application Circuit with $C1 = 1.5\text{pF}$, see Table 1 for details (Note 5)	3000		3900	
LO Frequency	f_{LO}	(Note 5)	2100		4000	MHz
IF Frequency	f_{IF}	Using Mini-Circuits TC4-1W-17 4:1 transformer as defined in the Typical Application Circuit, IF matching components affect the IF frequency range (Note 5)	100		500	MHz
		Using Mini-Circuits TC4-1W-7A 4:1 transformer as defined in the Typical Application Circuit, IF matching components affect the IF frequency range (Note 5)	50		250	
LO Drive	P_{LO}		-3	0	+3	dBm

5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 2300\text{MHz}$ TO 2900MHz , HIGH-SIDE LO INJECTION

(Typical Application Circuit with tuning elements outlined in **Table 1**, $V_{CC} = 4.75\text{V}$ to 5.25V , RF and LO ports are driven from 50Ω sources, $P_{LO} = -3\text{dBm}$ to $+3\text{dBm}$, $P_{RF} = -5\text{dBm}$, $f_{RF} = 2300\text{MHz}$ to 2900MHz , $f_{IF} = 300\text{MHz}$, $f_{LO} = 2600\text{MHz}$ to 3200MHz , $f_{RF} < f_{LO}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 2600\text{MHz}$, $f_{LO} = 2900\text{MHz}$, $f_{IF} = 300\text{MHz}$. All parameters are guaranteed by design and characterization, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small-Signal Conversion Gain		$f_{RF} = 2300\text{MHz}$ to 2900MHz , $T_C = +25^\circ\text{C}$ (Note 7)	7.9	8.7	9.2	dB
Gain Variation vs. Frequency	ΔG_C	$f_{RF} = 2305\text{MHz}$ to 2360MHz		0.1		dB
		$f_{RF} = 2500\text{MHz}$ to 2570MHz		0.1		
		$f_{RF} = 2570\text{MHz}$ to 2620MHz		0.1		
		$f_{RF} = 2500\text{MHz}$ to 2690MHz		0.2		
		$f_{RF} = 2700\text{MHz}$ to 2900MHz		0.3		
Conversion Gain Temperature Coefficient	TC_{CG}	$T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		-0.012		dB/ $^\circ\text{C}$
Single Sideband Noise Figure	NF_{SSB}	No blockers present		9.8	12	dB
		$f_{RF} = 2600\text{MHz}$, $f_{IF} = 300\text{MHz}$, $P_{LO} = 0\text{dBm}$, $V_{CC} = +5.0\text{V}$, $T_C = +25^\circ\text{C}$, no blockers present		9.8	10.5	
Noise Figure Temperature Coefficient	TC_{NF}	$f_{RF} = 2300\text{MHz}$ to 2900MHz , single sideband, no blockers present, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		0.018		dB/ $^\circ\text{C}$
Noise Figure Under Blocking	NF_B	+8dBm blocker tone applied to RF port, $f_{RF} = 2600\text{MHz}$, $f_{LO} = 2900\text{MHz}$, $f_{BLOCKER} = 2400\text{MHz}$, $P_{LO} = 0\text{dBm}$, $V_{CC} = +5.0\text{V}$, $T_C = +25^\circ\text{C}$ (Note 8)		18	22	dB

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5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 2300\text{MHz}$ TO 2900MHz , HIGH-SIDE LO INJECTION (continued)

(Typical Application Circuit with tuning elements outlined in **Table 1**, $V_{CC} = 4.75\text{V}$ to 5.25V , RF and LO ports are driven from 50Ω sources, $P_{LO} = -3\text{dBm}$ to $+3\text{dBm}$, $P_{RF} = -5\text{dBm}$, $f_{RF} = 2300\text{MHz}$ to 2900MHz , $f_{IF} = 300\text{MHz}$, $f_{LO} = 2600\text{MHz}$ to 3200MHz , $f_{RF} < f_{LO}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 2600\text{MHz}$, $f_{LO} = 2900\text{MHz}$, $f_{IF} = 300\text{MHz}$. All parameters are guaranteed by design and characterization, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input 1dB Compression Point	IP _{1dB}	$T_C = +25^\circ\text{C}$ (Note 9)	9.5	11		dBm
		$f_{RF} = 2600\text{MHz}$ $T_C = +25^\circ\text{C}$ (Notes 7, 9)	10	11		
Third-Order Input Intercept Point	IIP ₃	$f_{RF1} - f_{RF2} = 1\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$, $T_C = +25^\circ\text{C}$ (Note 7)	22.5	24.5		dBm
IIP ₃ Variation with T_C		$f_{RF} = 2300\text{MHz}$ to 2900MHz , $f_{RF1} - f_{RF2} = 1\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		± 0.3		dB
2LO-2RF Spur Rejection	2 x 2	$f_{SPUR} = f_{LO} - 150\text{MHz}$	$P_{RF} = -10\text{dBm}$	60	67	dBc
			$P_{RF} = -5\text{dBm}$	55	62	
3LO-3RF Spur Rejection	3 x 3	$f_{SPUR} = f_{LO} - 100\text{MHz}$	$P_{RF} = -10\text{dBm}$	75	85	dBc
			$P_{RF} = -5\text{dBm}$	65	75	
RF Input Return Loss	RL _{RF}	LO on and IF terminated into a matched impedance		17.5		dB
LO Input Return Loss	RL _{LO}	RF and IF terminated into a matched impedance		19.5		dB
IF Output Impedance	Z _{IF}	Nominal differential impedance at the IC's IF outputs		200		Ω
IF Output Return Loss	RL _{IF}	RF terminated into 50Ω , LO driven by 50Ω source, IF transformed to 50Ω using external components shown in the <i>Typical Application Circuit</i> ; see the <i>Typical Operating Characteristics</i> for performance vs. inductor values	$f_{IF} = 450\text{MHz}$, $L1 = L2 = 120\text{nH}$	25		dB
			$f_{IF} = 350\text{MHz}$, $L1 = L2 = 270\text{nH}$	25		
			$f_{IF} = 300\text{MHz}$, $L1 = L2 = 390\text{nH}$	25		
RF-to-IF Isolation		$P_{LO} = +3\text{dBm}$ (Note 7)	27	30		dB
LO Leakage at RF Port		$P_{LO} = +3\text{dBm}$	-28.6	-22.8		dBm
2LO Leakage at RF Port		$P_{LO} = +3\text{dBm}$	-29.7			dBm
LO Leakage at IF Port		$P_{LO} = +3\text{dBm}$ (Note 7)	-28.4			dBm

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3.3V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 2300\text{MHz}$ TO 2900MHz , HIGH-SIDE LO INJECTION

(Typical Application Circuit with tuning elements outlined in **Table 1**, RF and LO ports are driven from 50Ω sources. Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 3.3\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 2600\text{MHz}$, $f_{LO} = 2900\text{MHz}$, $f_{IF} = 300\text{MHz}$, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Small-Signal Conversion Gain	G_C				8.3		dB
Gain Variation vs. Frequency	ΔG_C	$f_{RF} = 2300\text{MHz}$ to 2900MHz , any 100MHz band			0.15		dB
Conversion Gain Temperature Coefficient	TC_{CG}	$T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$			-0.012		dB/ $^\circ\text{C}$
Single Sideband Noise Figure	NF_{SSB}	No blockers present			9.6		dB
Noise Figure Temperature Coefficient	TC_{NF}	Single sideband, no blockers present, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$			0.018		dB/ $^\circ\text{C}$
Input 1dB Compression Point	IP_{1dB}	(Note 9)			7.75		dBm
Third-Order Input Intercept Point	$IIP3$	$f_{RF1} = 2600\text{MHz}$, $f_{RF2} = 2601\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$			19.7		dBm
IIP3 Variation with T_C		$f_{RF1} = 2600\text{MHz}$, $f_{RF2} = 2601\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$			± 0.5		dB
2LO-2RF Spur Rejection	2×2	$f_{SPUR} = f_{LO} - 150\text{MHz}$	$P_{RF} = -10\text{dBm}$		64		dBc
			$P_{RF} = -5\text{dBm}$		59		
3LO-3RF Spur Rejection	3×3	$f_{SPUR} = f_{LO} - 100\text{MHz}$	$P_{RF} = -10\text{dBm}$		74		dBc
			$P_{RF} = -5\text{dBm}$		64		
RF Input Return Loss	RL_{RF}	LO on and IF terminated into a matched impedance			17.5		dB
LO Input Return Loss	RL_{LO}	RF and IF terminated into a matched impedance			19.5		dB
IF Output Impedance	Z_{IF}	Nominal differential impedance at the IC's IF outputs			200		Ω
IF Output Return Loss	RL_{IF}	RF terminated into 50Ω , LO driven by 50Ω source, IF transformed to 50Ω using external components shown in the <i>Typical Application Circuit</i> ; see the <i>Typical Operating Characteristics</i> for performance vs. inductor values	$f_{IF} = 450\text{MHz}$, $L1 = L2 = 120\text{nH}$		25		dB
			$f_{IF} = 350\text{MHz}$, $L1 = L2 = 270\text{nH}$		25		
			$f_{IF} = 300\text{MHz}$, $L1 = L2 = 390\text{nH}$		25		
RF-to-IF Isolation		$f_{RF} = 2300\text{MHz}$ to 2900MHz , $P_{LO} = +3\text{dBm}$			38		dB
LO Leakage at RF Port		$f_{LO} = 2600\text{MHz}$ to 3200MHz , $P_{LO} = +3\text{dBm}$			-30		dBm
2LO Leakage at RF Port		$f_{LO} = 2600\text{MHz}$ to 3200MHz , $P_{LO} = +3\text{dBm}$			-31		dBm
LO Leakage at IF Port		$f_{LO} = 2600\text{MHz}$ to 3200MHz , $P_{LO} = +3\text{dBm}$			-34		dBm

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5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— f_{RF} = 2300MHz TO 2900MHz, LOW-SIDE LO INJECTION

(Typical Application Circuit with tuning elements outlined in **Table 1**, V_{CC} = 4.75V to 5.25V, RF and LO ports are driven from 50 Ω sources. P_{LO} = -3dBm to +3dBm, P_{RF} = -5dBm, f_{RF} = 2300MHz to 2900MHz, f_{IF} = 300MHz, f_{LO} = 2000MHz to 2600MHz, $f_{RF} > f_{LO}$, T_C = -40°C to +85°C. Typical values are for T_C = +25°C, V_{CC} = 5.0V, P_{LO} = 0dBm, f_{RF} = 2600MHz, f_{LO} = 2300MHz, f_{IF} = 300MHz, all parameters are guaranteed by design and characterization, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small-Signal Conversion Gain	G_C	f_{RF} = 2300MHz to 2900MHz, T_C = +25°C (Note 7)	8.2	8.9	9.5	dB
Gain Variation vs. Frequency	ΔG_C	f_{RF} = 2300MHz to 2900MHz, any 100MHz band		0.1		dB
Conversion Gain Temperature Coefficient	TC_{CG}	T_C = -40°C to +85°C		-0.012		dB/°C
Single Sideband Noise Figure	NF_{SSB}	No blockers present		9.5	12.5	dB
		f_{RF} = 2600MHz, f_{IF} = 300MHz, P_{LO} = 0dBm, V_{CC} = +5.0V, T_C = +25°C, no blockers present		9.5	10.5	
Noise Figure Temperature Coefficient	TC_{NF}	Single sideband, no blockers present, T_C = -40°C to +85°C		0.018		dB/°C
Input 1dB Compression Point	IP_{1dB}	T_C = +25°C (Note 9)	9.5	10.7		dBm
Third-Order Input Intercept Point	$IIP3$	$f_{RF1} - f_{RF2}$ = 1MHz, $P_{RF1} = P_{RF2}$ = -5dBm, T_C = +25°C (Note 7)	22	24.05		dBm
IIP3 Variation with T_C		f_{RF} = 2300MHz to 2900MHz, $P_{RF1} = P_{RF2}$ = -5dBm, T_C = -40°C to +85°C		± 0.5		dB
2RF-2LO Spur Rejection	2 x 2	$f_{SPUR} = f_{LO} + 150MHz$	$P_{RF} = -10dBm$	63	68	dBc
			$P_{RF} = -5dBm$	58	63	
3RF-3LO Spur Rejection	3 x 3	$f_{SPUR} = f_{LO} + 100MHz$	$P_{RF} = -10dBm$	79	84	dBc
			$P_{RF} = -5dBm$	69	74	
RF Input Return Loss	RL_{RF}	LO on and IF terminated into a matched impedance		19		dB
LO Input Return Loss	RL_{LO}	RF and IF terminated into a matched impedance		18		dB
IF Output Impedance	Z_{IF}	Nominal differential impedance at the IC's IF outputs		200		Ω
IF Output Return Loss	RL_{IF}	RF terminated into 50 Ω , LO driven by 50 Ω source, IF transformed to 50 Ω using external components shown in the <i>Typical Application Circuit</i> ; see the <i>Typical Operating Characteristics</i> for performance vs. inductor values	$f_{IF} = 450MHz$, $L1 = L2 = 120nH$	25		dB
			$f_{IF} = 350MHz$, $L1 = L2 = 270nH$	25		
			$f_{IF} = 300MHz$, $L1 = L2 = 390nH$	25		
RF-to-IF Isolation		f_{RF} = 2600MHz, P_{LO} = +3dBm	29	36		dB
LO Leakage at RF Port		f_{LO} = 1800MHz to 2900MHz, P_{LO} = +3dBm		-28	-20	dBm
2LO Leakage at RF Port		f_{LO} = 1800MHz to 2900MHz, P_{LO} = +3dBm		-29	-19	dBm
LO Leakage at IF Port		f_{LO} = 1800MHz to 2900MHz, P_{LO} = +3dBm		-24		dBm

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5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 3100\text{MHz}$ TO 3900MHz , LOW-SIDE LO INJECTION

(Typical Application Circuit with tuning elements outlined in **Table 1**, $V_{CC} = 4.75\text{V}$ to 5.25V , RF and LO ports are driven from 50Ω sources, $P_{LO} = -3\text{dBm}$ to $+3\text{dBm}$, $P_{RF} = -5\text{dBm}$, $f_{RF} = 3100\text{MHz}$ to 3900MHz , $f_{IF} = 300\text{MHz}$, $f_{LO} = 2800\text{MHz}$ to 3600MHz , $f_{RF} > f_{LO}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 3500\text{MHz}$, $f_{LO} = 3200\text{MHz}$, $f_{IF} = 300\text{MHz}$. All parameters are guaranteed by design and characterization, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Small-Signal Conversion Gain	G _C	T _C = +25°C (Note 7)		7.5	8.0	8.5	dB
Gain Variation vs. Frequency	ΔG _C	f _{RF} = 3450MHz to 3750MHz, any 100MHz band		0.15			dB
		f _{RF} = 3450MHz to 3750MHz, any 200MHz band		0.3			
Conversion Gain Temperature Coefficient	TC _{CG}	T _C = -40°C to +85°C		-0.012			dB/°C
Single Sideband Noise Figure	NF _{SSB}	No blockers present		10.5	13.5		dB
		f _{RF} = 3500MHz, f _{IF} = 300MHz, P _{LO} = 0dBm, V _{CC} = +5.0V, T _C = +25°C, no blockers present		10.5	11.6		
Noise Figure Temperature Coefficient	TC _{NF}	f _{RF} = 3100MHz to 3900MHz, single sideband, no blockers present, T _C = -40°C to +85°C		0.018			dB/°C
Noise Figure Under Blocking	NF _B	+8dBm blocker tone applied to RF port, f _{RF} = 3500MHz, f _{LO} = 3200MHz, f _{BLOCKER} = 3750MHz, P _{LO} = 0dBm, V _{CC} = +5.0V, T _C = +25°C (Note 8)		18.7	21		dB
Input 1dB Compression Point	IP _{1dB}	f _{RF} = 3500MHz (Note 9)		10	12		dBm
Third-Order Input Intercept Point	IIP ₃	f _{RF1} - f _{RF2} = 1MHz, P _{RF1} = P _{RF2} = -5dBm (Note 7)		23	25		dBm
IIP ₃ Variation with T _C		f _{RF} = 3100MHz to 3900MHz, f _{IF} = 300MHz, f _{RF1} - f _{RF2} = 1MHz, P _{RF1} = P _{RF2} = -5dBm, T _C = -40°C to +85°C		±0.3			dB
2RF-2LO Spur Rejection	2 x 2	f _{SPUR} = f _{LO} + 150MHz	P _{RF} = -10dBm	60	69		dBc
			P _{RF} = -5dBm	55	64		
3RF-3LO Spur Rejection	3 x 3	f _{SPUR} = f _{LO} + 100MHz	P _{RF} = -10dBm	78	86		dBc
			P _{RF} = -5dBm	68	76		
RF Input Return Loss	RL _{RF}	LO on and IF terminated into a matched impedance		20			dB
LO Input Return Loss	RL _{LO}	RF and IF terminated into a matched impedance		16.5			dB
IF Output Impedance	Z _{IF}	Nominal differential impedance at the IC's IF outputs		200			Ω

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5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 3100\text{MHz}$ TO 3900MHz , LOW-SIDE LO INJECTION (continued)

(Typical Application Circuit with tuning elements outlined in **Table 1**, $V_{CC} = 4.75\text{V}$ to 5.25V , RF and LO ports are driven from 50Ω sources, $P_{LO} = -3\text{dBm}$ to $+3\text{dBm}$, $P_{RF} = -5\text{dBm}$, $f_{RF} = 3100\text{MHz}$ to 3900MHz , $f_{IF} = 300\text{MHz}$, $f_{LO} = 2800\text{MHz}$ to 3600MHz , $f_{RF} > f_{LO}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 3500\text{MHz}$, $f_{LO} = 3200\text{MHz}$, $f_{IF} = 300\text{MHz}$. All parameters are guaranteed by design and characterization, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
IF Output Return Loss	RL_{IF}	RF terminated into 50Ω , LO driven by 50Ω source, IF transformed to 50Ω using external components shown in the <i>Typical Application Circuit</i> ; see the <i>Typical Operating Characteristics</i> for performance vs. inductor values	$f_{IF} = 450\text{MHz}$, $L1 = L2 = 120\text{nH}$	25		dB
			$f_{IF} = 350\text{MHz}$, $L1 = L2 = 270\text{nH}$	25		
			$f_{IF} = 300\text{MHz}$, $L1 = L2 = 390\text{nH}$	25		
RF-to-IF Isolation		$f_{RF} = 2600\text{MHz}$ $P_{LO} = +3\text{dBm}$ (Note 7)	23	27		dB
LO Leakage at RF Port		$f_{LO} = 2800\text{MHz}$ to 3600MHz $P_{LO} = +3\text{dBm}$		-31	-20	dBm
2LO Leakage at RF Port		$P_{LO} = +3\text{dBm}$		-27		dBm
LO Leakage at IF Port		$P_{LO} = +3\text{dBm}$ (Note 7)		-29.5	-20	dBm

+5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— $f_{RF} = 3100\text{MHz}$ TO 3900MHz , HIGH-SIDE LO INJECTION

(Typical Application Circuit with tuning elements outlined in **Table 1**, $V_{CC} = 4.75\text{V}$ to 5.25V , RF and LO ports are driven from 50Ω sources, Typical values are for $T_C = +25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $P_{LO} = 0\text{dBm}$, $f_{RF} = 3500\text{MHz}$, $f_{LO} = 3800\text{MHz}$, $f_{IF} = 300\text{MHz}$. Parameters are guaranteed by design and not production tested.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small-Signal Conversion Gain	G_C			7.6		dB
Gain Variation vs. Frequency	ΔG_C	$f_{RF} = 3450\text{MHz}$ to 3750MHz , any 100MHz band		0.15		dB
		$f_{RF} = 3450\text{MHz}$ to 3750MHz , any 200MHz band		0.3		
Conversion Gain Temperature Coefficient	TC_{CG}	$T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		-0.012		dB/ $^\circ\text{C}$
Single Sideband Noise Figure	NF_{SSB}	No blockers present		10.9		dB
Noise Figure Temperature Coefficient	TC_{NF}	Single sideband, no blockers present, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		0.018		dB/ $^\circ\text{C}$
Input 1dB Compression Point	IP_{1dB}	(Note 9)		12.4		dBm
Third-Order Input Intercept Point	$IIP3$	$f_{RF1} = 3500\text{MHz}$, $f_{RF2} = 3501\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$		24.7		dBm
IIP3 Variation with T_C		$f_{RF1} = 3500\text{MHz}$, $f_{RF2} = 3501\text{MHz}$, $P_{RF1} = P_{RF2} = -5\text{dBm}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$		± 0.5		dB
2LO-2RF Spur Rejection	2×2	$f_{SPUR} = f_{LO} - 150\text{MHz}$	$P_{RF} = -10\text{dBm}$	69		dBc
			$P_{RF} = -5\text{dBm}$	64		

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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+5.0V SUPPLY AC ELECTRICAL CHARACTERISTICS— f_{RF} = 3100MHz TO 3900MHz, HIGH-SIDE LO INJECTION (continued)

(Typical Application Circuit with tuning elements outlined in **Table 1**, V_{CC} = 4.75V to 5.25V, RF and LO ports are driven from 50 Ω sources, Typical values are for T_C = +25°C, V_{CC} = 5.0V, P_{LO} = 0dBm, f_{RF} = 3500MHz, f_{LO} = 3800MHz, f_{IF} = 300MHz. Parameters are guaranteed by design and not production tested.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
3LO-3RF Spur Rejection	3 x 3	$f_{SPUR} = f_{LO} - 100\text{MHz}$	$P_{RF} = -10\text{dBm}$		90		dBc
			$P_{RF} = -5\text{dBm}$		80		
RF Input Return Loss	RL_{RF}	LO on and IF terminated into a matched impedance			22		dB
LO Input Return Loss	RL_{LO}	RF and IF terminated into a matched impedance			16.3		dB
IF Output Impedance	Z_{IF}	Nominal differential impedance at the IC's IF outputs			200		Ω
IF Output Return Loss	RL_{IF}	RF terminated into 50 Ω , LO driven by 50 Ω source, IF transformed to 50 Ω using external components shown in the <i>Typical Application Circuit</i> ; see the <i>Typical Operating Characteristics</i> for performance vs. inductor values	$f_{IF} = 450\text{MHz}$, $L1 = L2 = 120\text{nH}$		25		dB
			$f_{IF} = 350\text{MHz}$, $L1 = L2 = 270\text{nH}$		25		
			$f_{IF} = 300\text{MHz}$, $L1 = L2 = 390\text{nH}$		25		
RF-to-IF Isolation		$f_{RF} = 3100\text{MHz}$ to 3700MHz , $P_{LO} = +3\text{dBm}$			26.6		dB
LO Leakage at RF Port		$f_{LO} = 3400\text{MHz}$ to 4000MHz , $P_{LO} = +3\text{dBm}$			-38		dBm
2LO Leakage at RF Port		$f_{LO} = 3400\text{MHz}$ to 4000MHz , $P_{LO} = +3\text{dBm}$			-13.5		dBm
LO Leakage at IF Port		$f_{LO} = 3400\text{MHz}$ to 4000MHz , $P_{LO} = +3\text{dBm}$			-27		dBm

Note 5: Not production tested. Operation outside this range is possible, but with degraded performance of some parameters. See the *Typical Operating Characteristics*.

Note 6: All limits reflect losses of external components, including a 0.8dB loss at $f_{IF} = 300\text{MHz}$ due to the 4:1 impedance transformer. Output measurements were taken at IF outputs of the *Typical Application Circuit*.

Note 7: 100% production tested for functional performance.

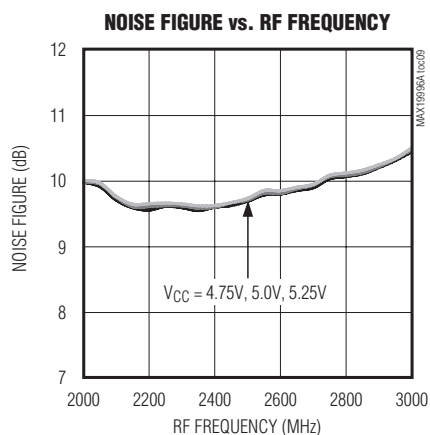
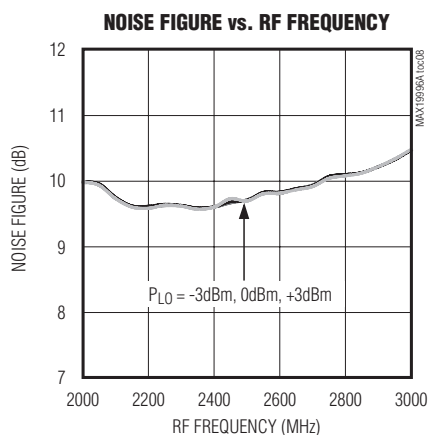
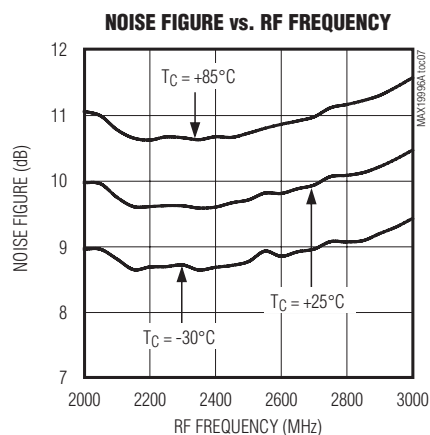
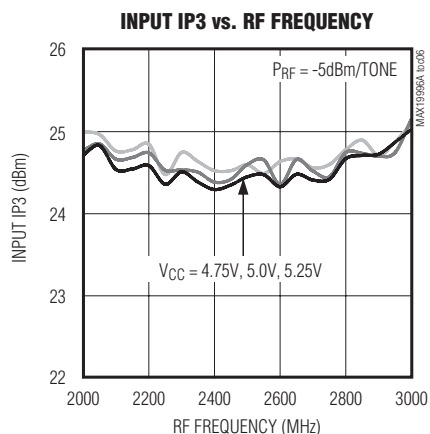
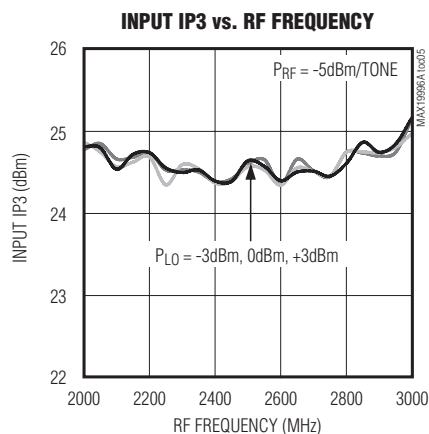
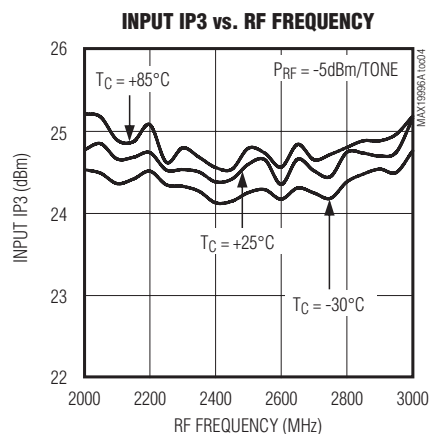
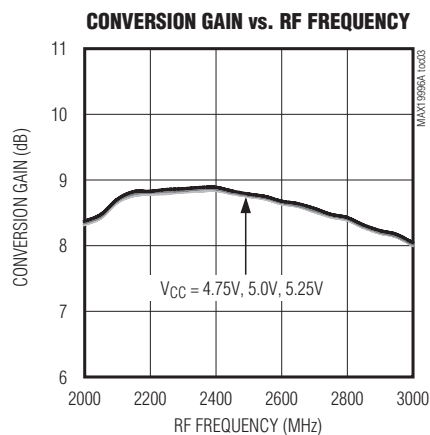
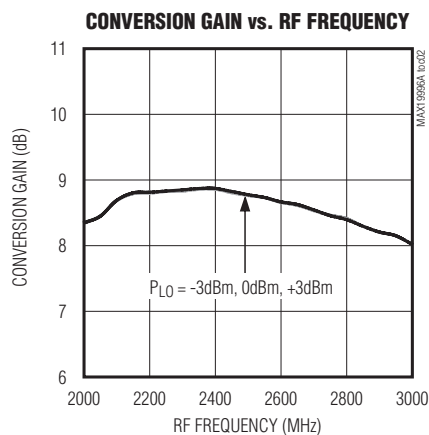
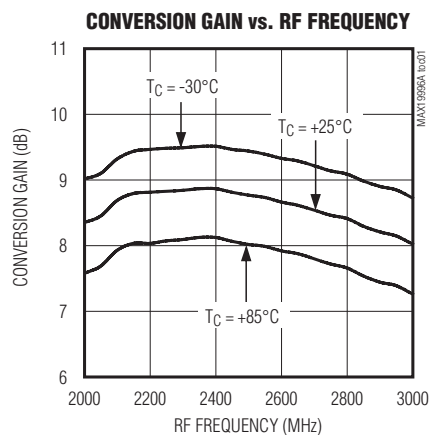
Note 8: Measured with external LO source noise filtered so that the noise floor is -174dBm/Hz. This specification reflects the effects of all SNR degradations in the mixer including the LO noise, as defined in Application Note 2021: *Specifications and Measurement of Local Oscillator Noise in Integrated Circuit Base Station Mixers*.

Note 9: Maximum reliable continuous input power applied to the RF port of this device is +12dBm from a 50 Ω source.

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

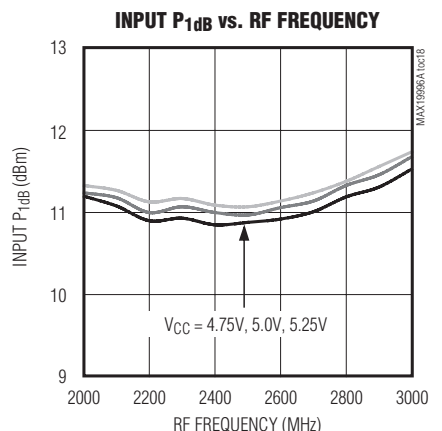
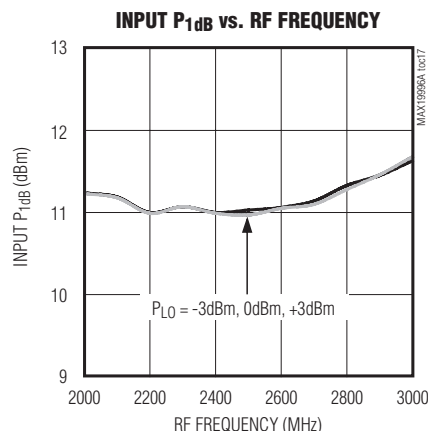
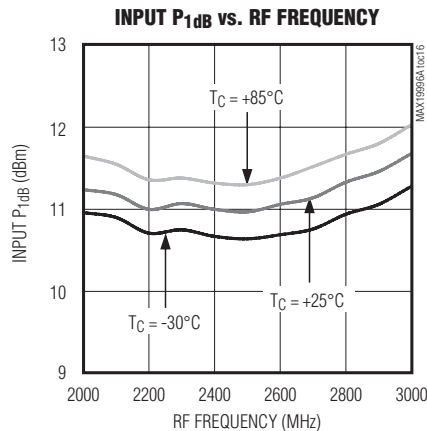
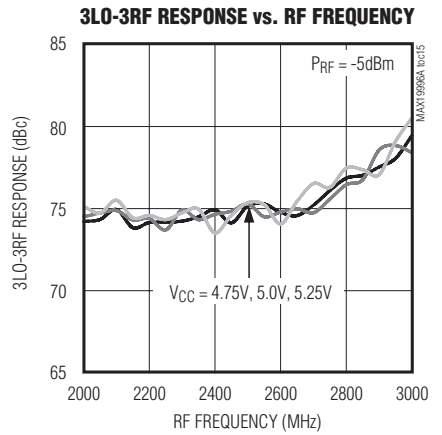
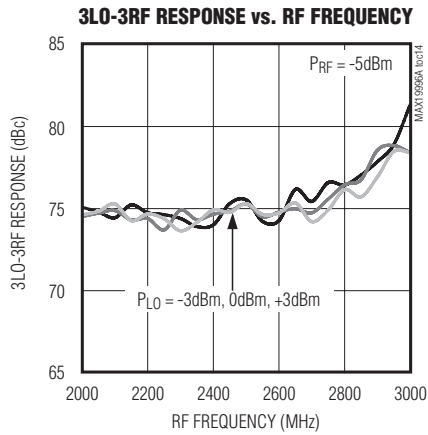
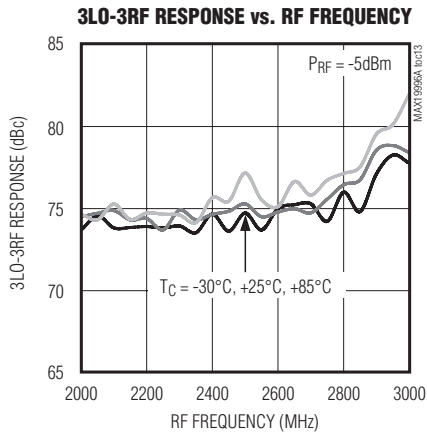
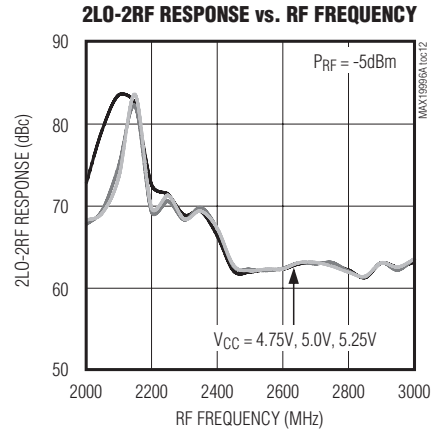
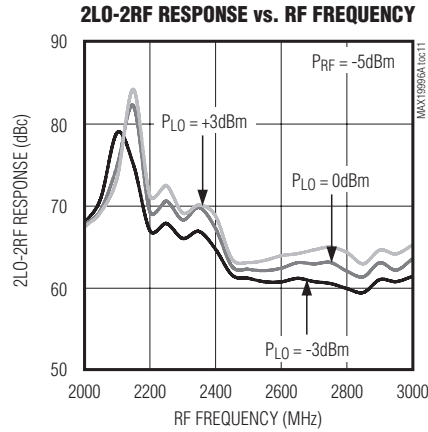
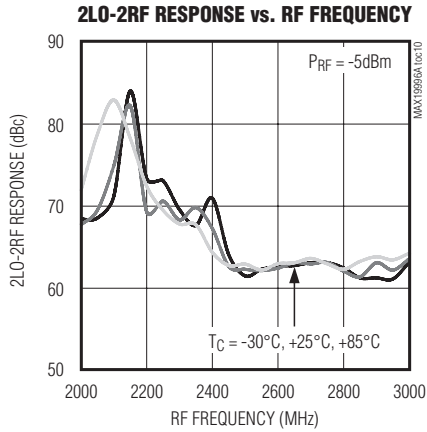


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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Typical Operating Characteristics (continued)

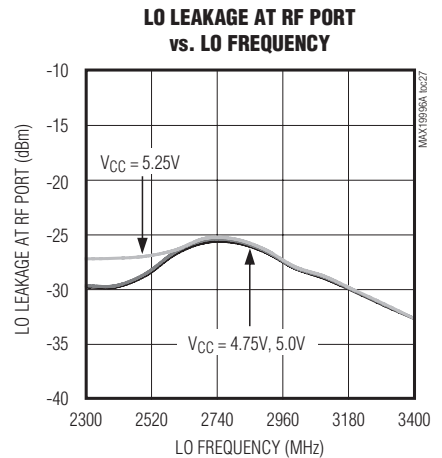
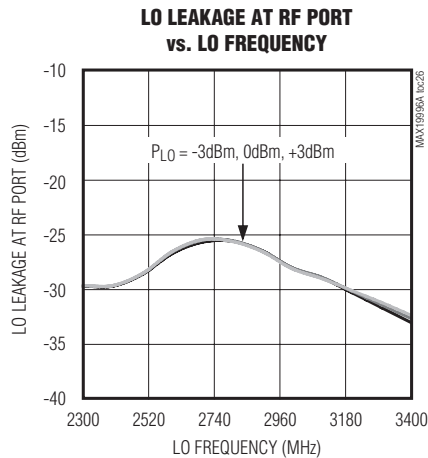
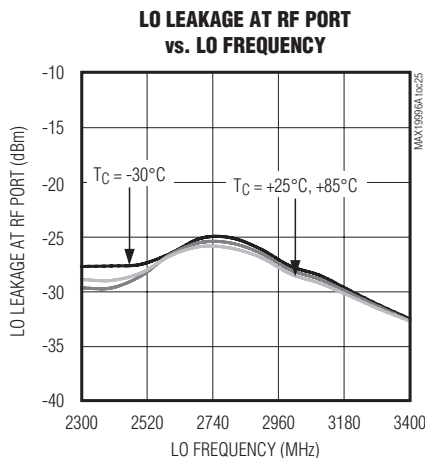
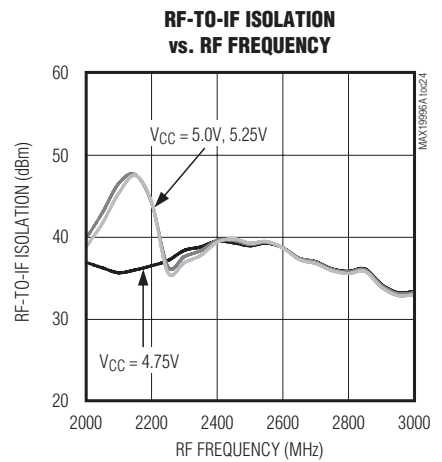
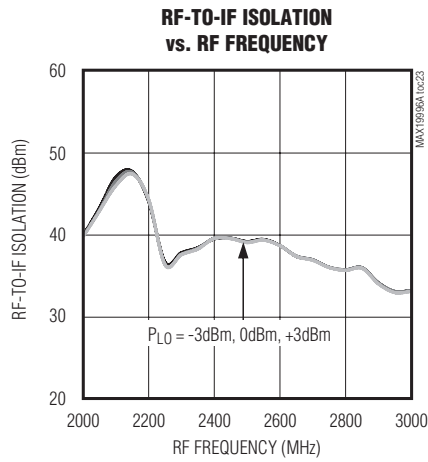
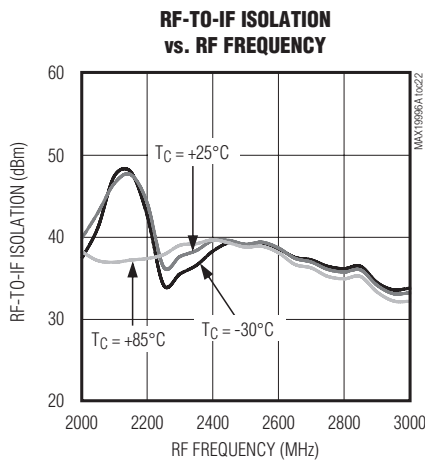
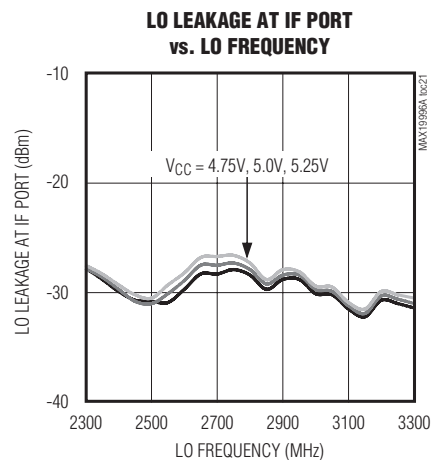
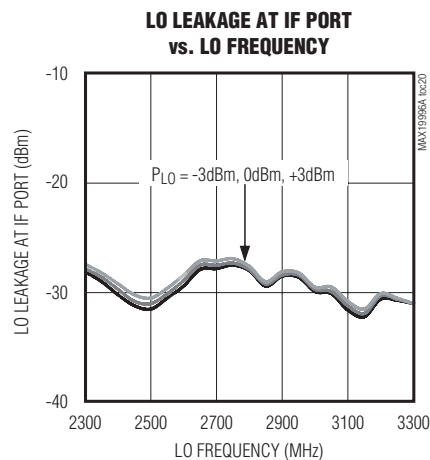
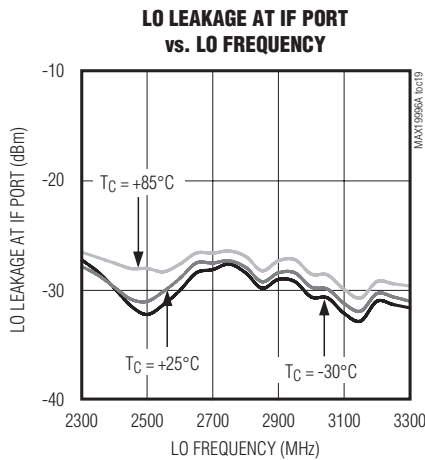
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

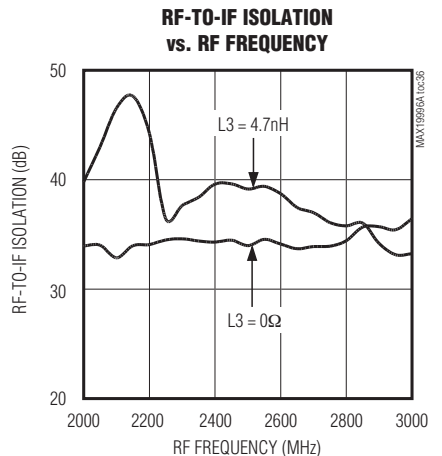
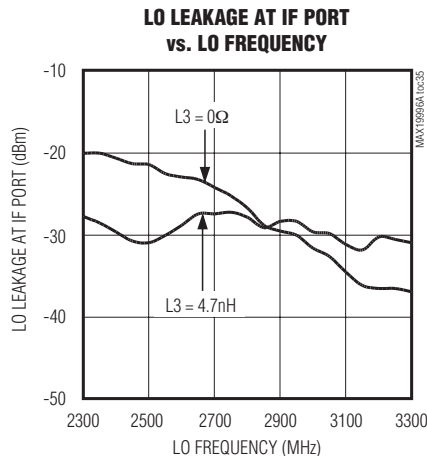
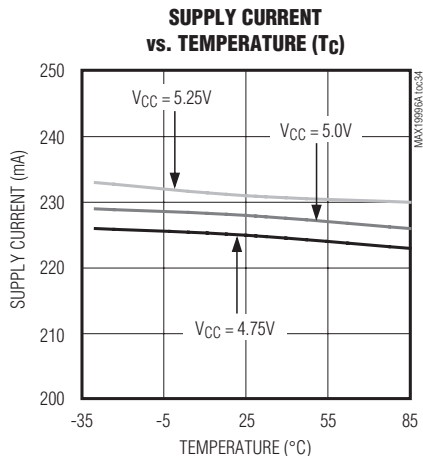
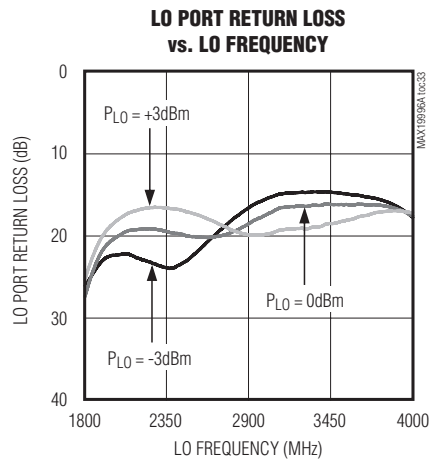
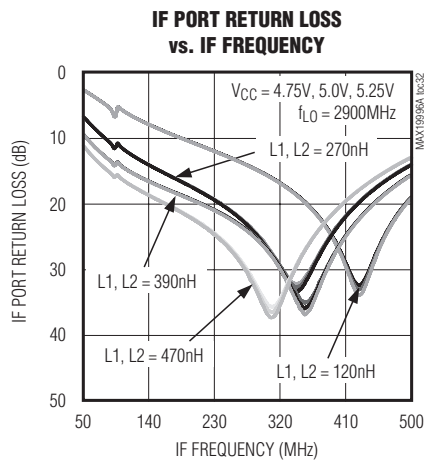
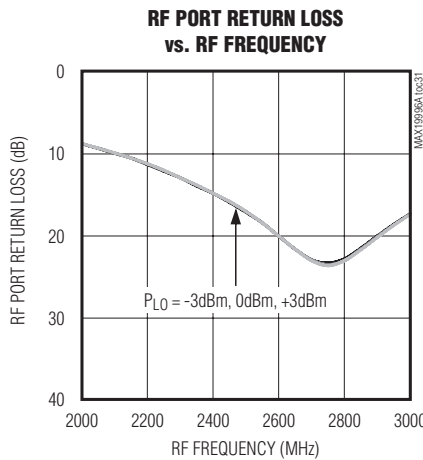
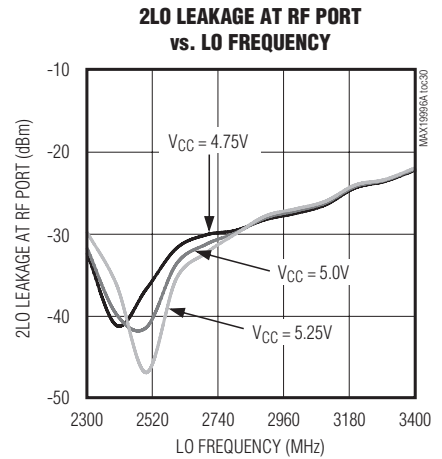
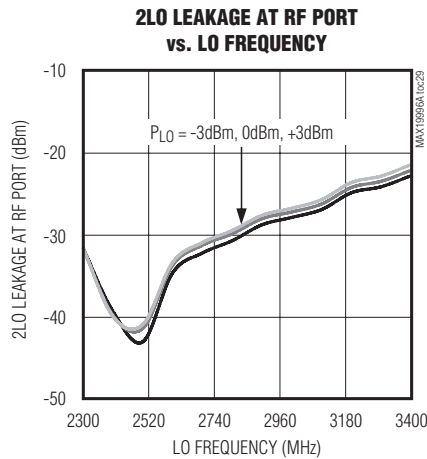
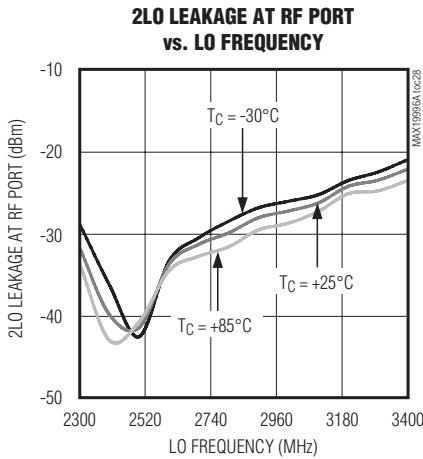


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

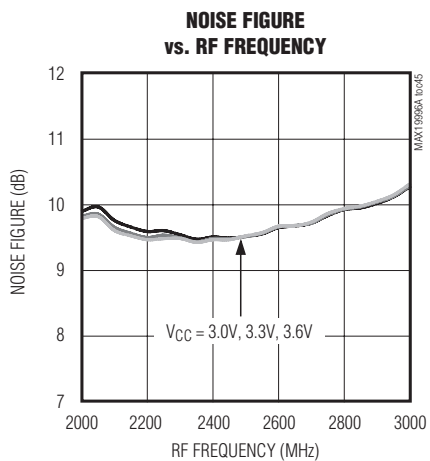
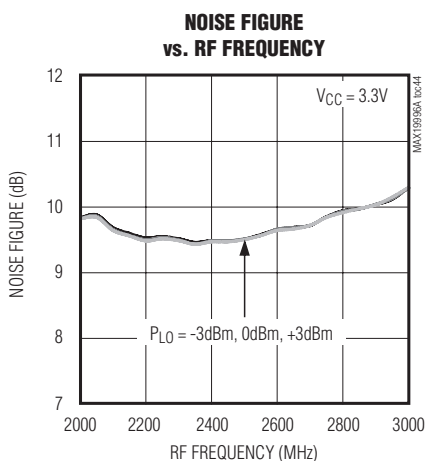
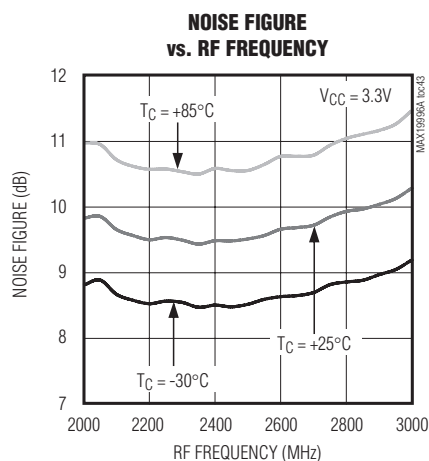
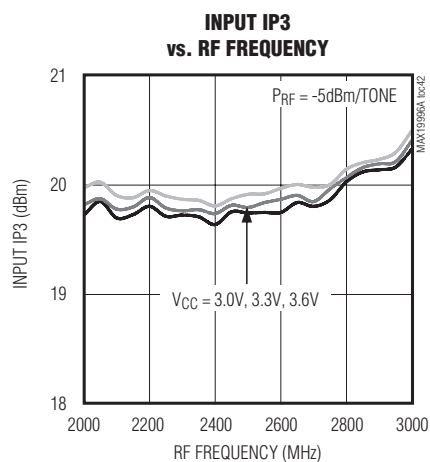
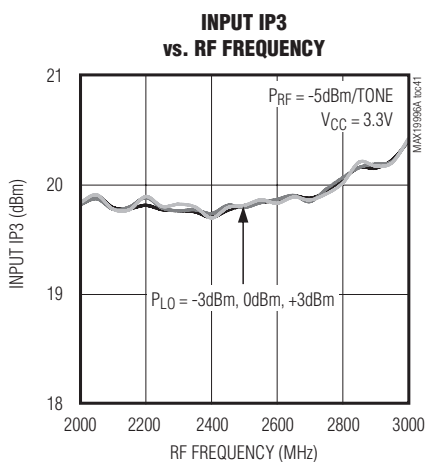
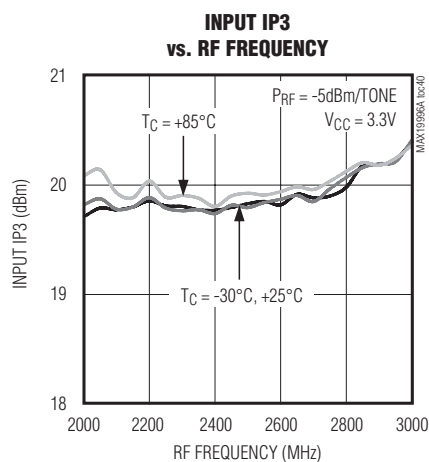
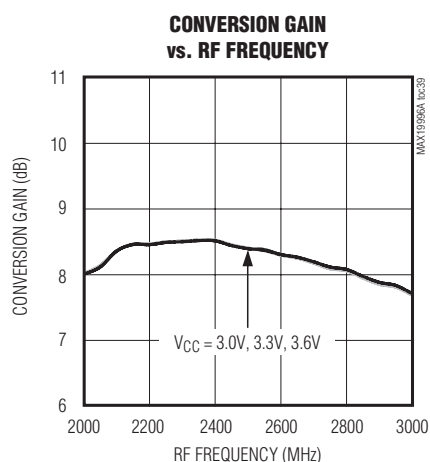
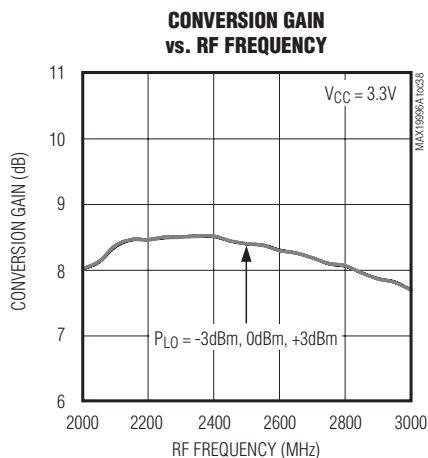
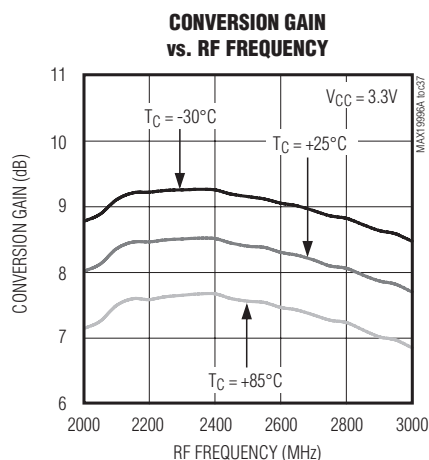
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SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 3.3V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

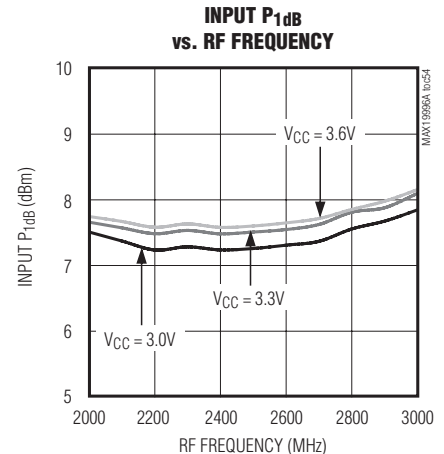
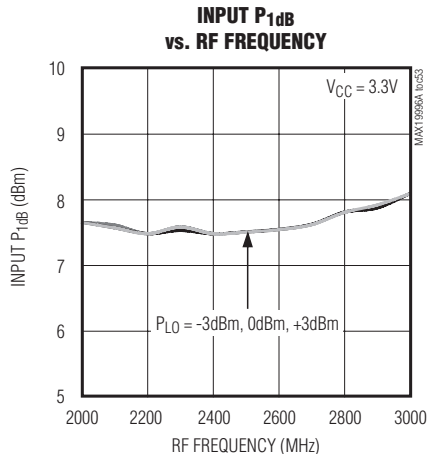
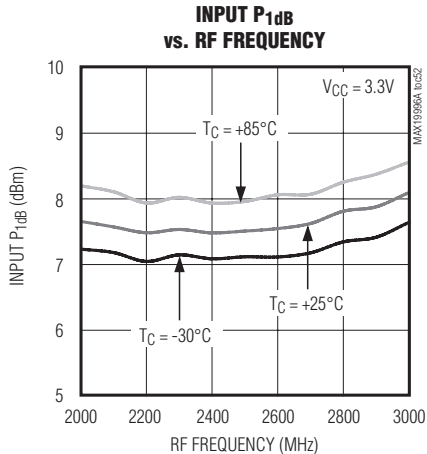
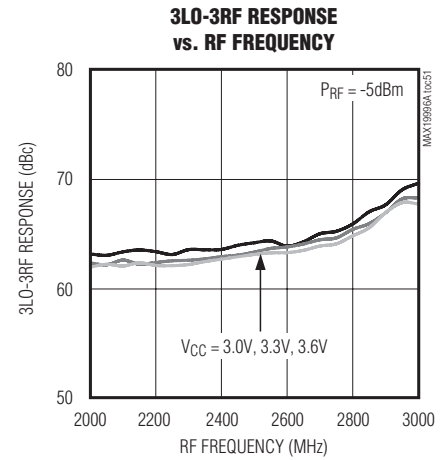
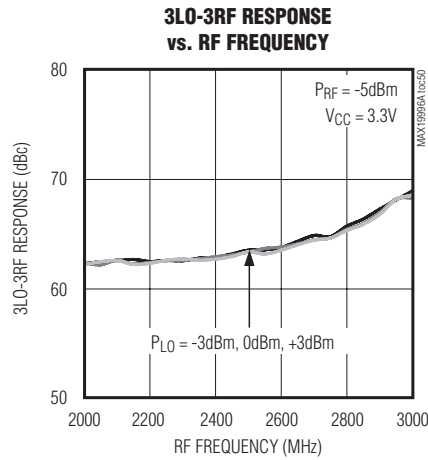
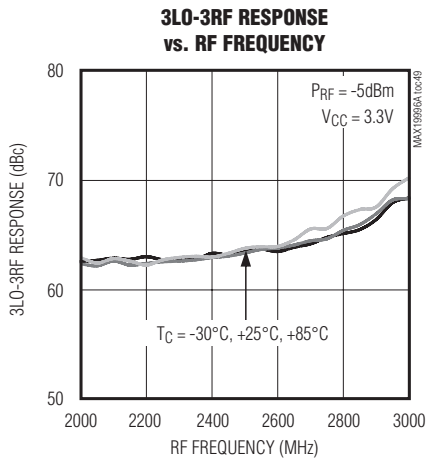
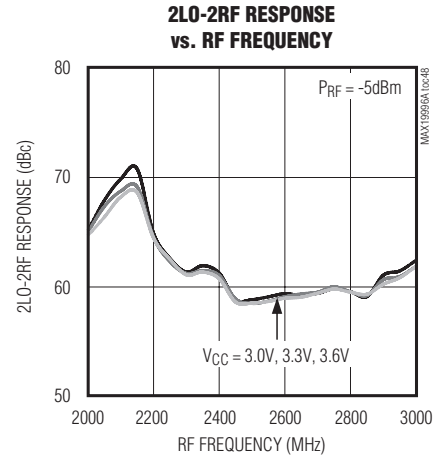
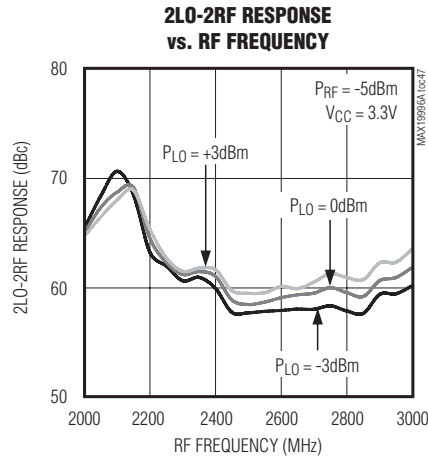
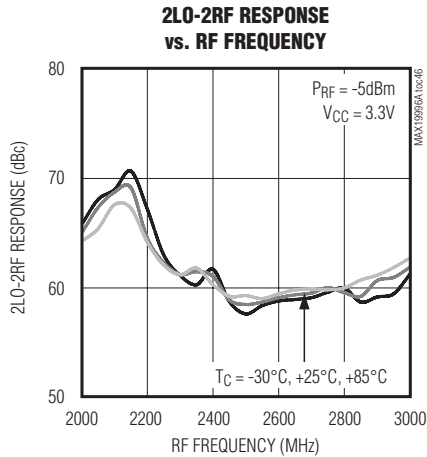


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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Typical Operating Characteristics (continued)

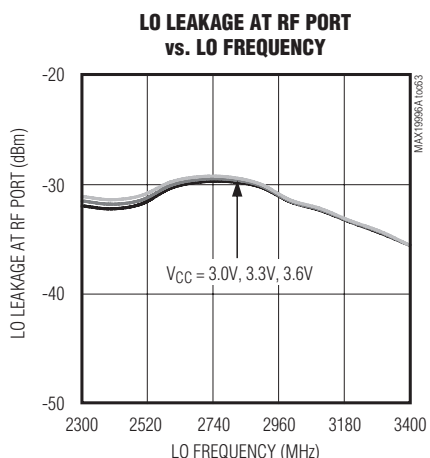
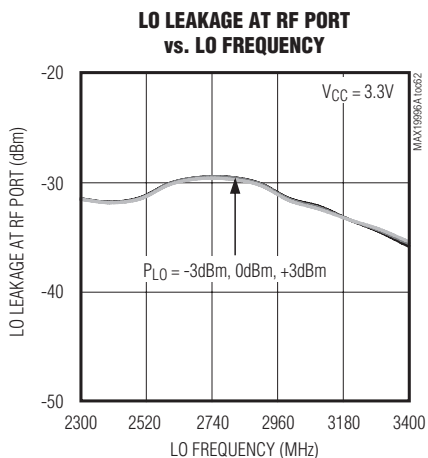
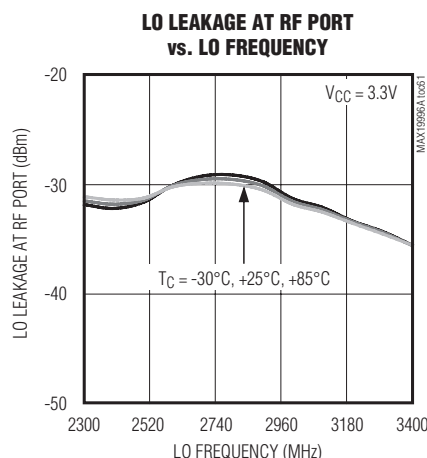
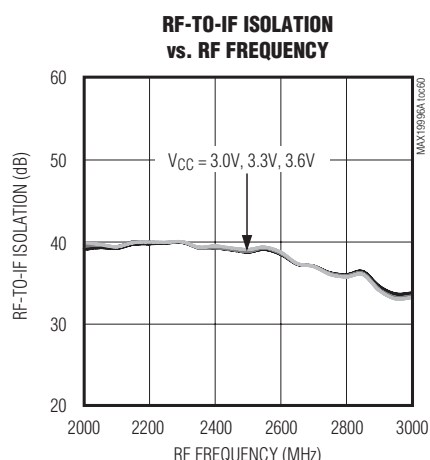
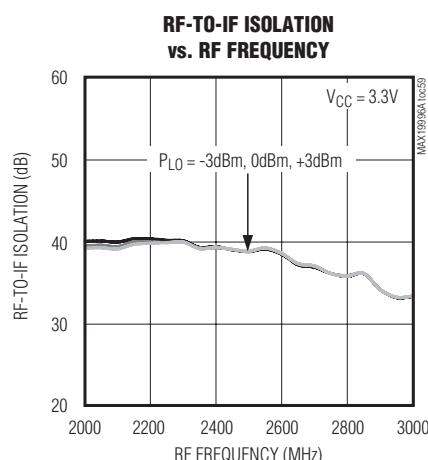
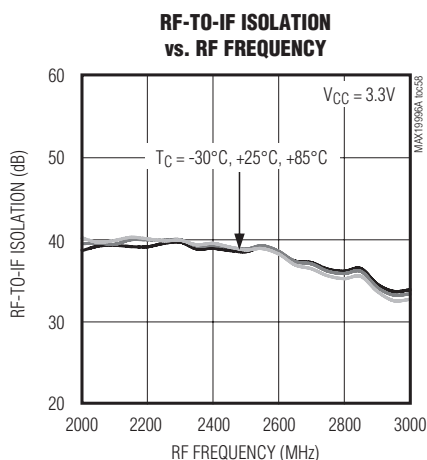
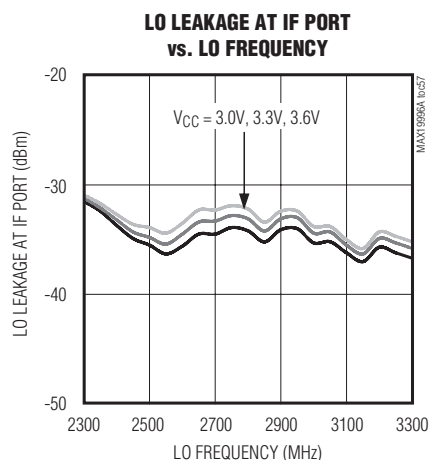
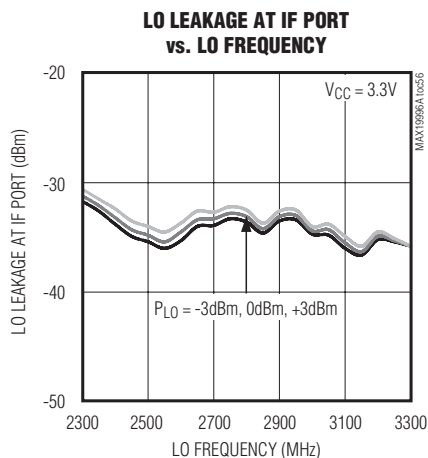
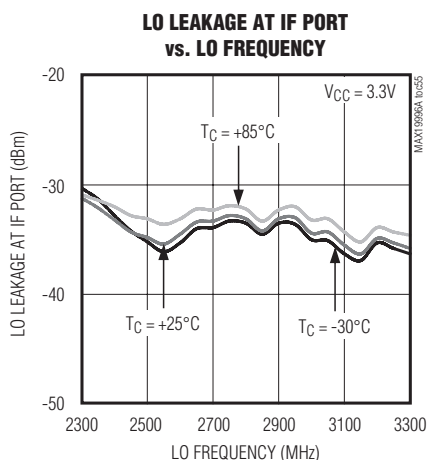
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 3.3V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 3.3V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

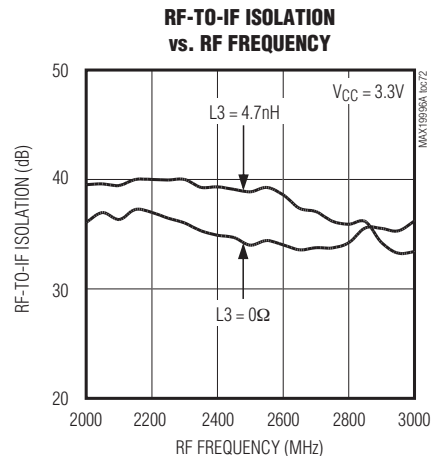
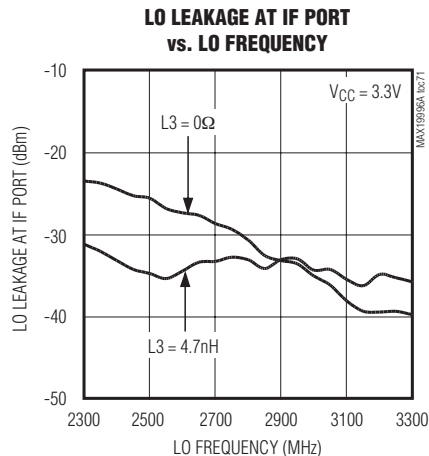
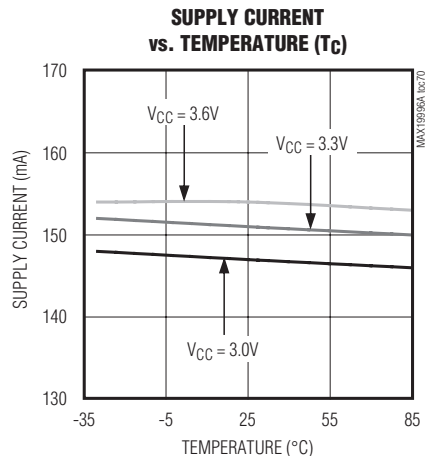
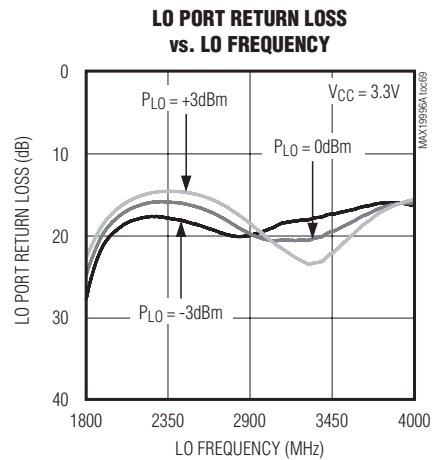
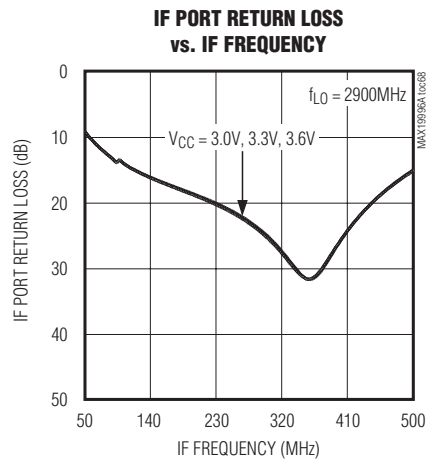
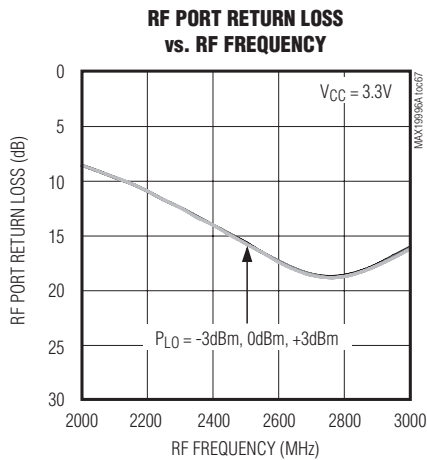
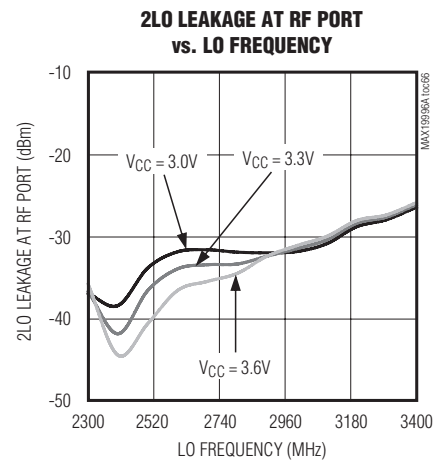
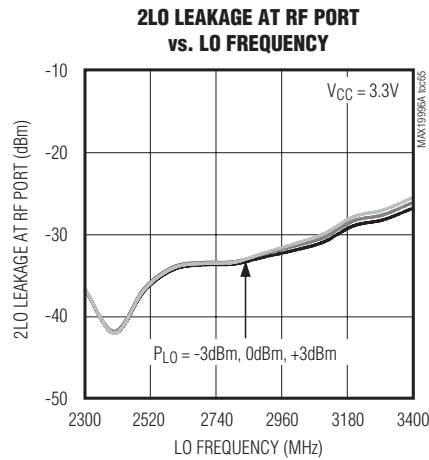
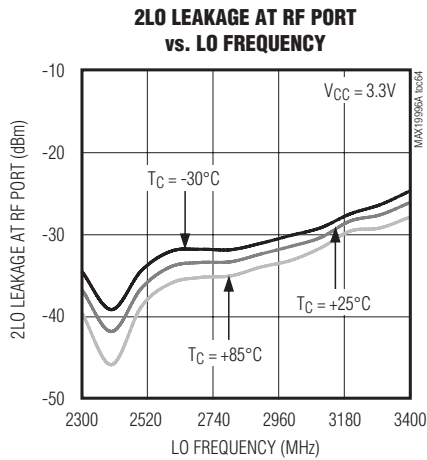


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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Typical Operating Characteristics (continued)

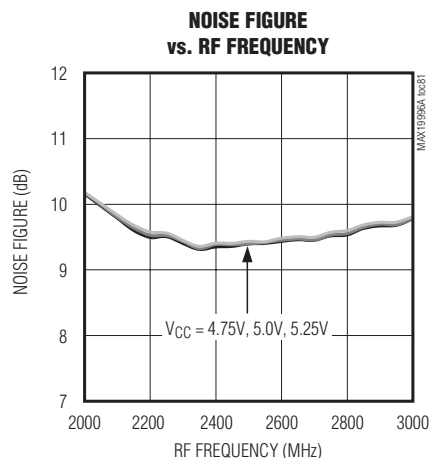
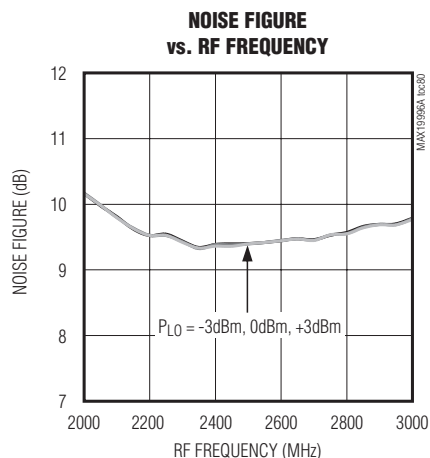
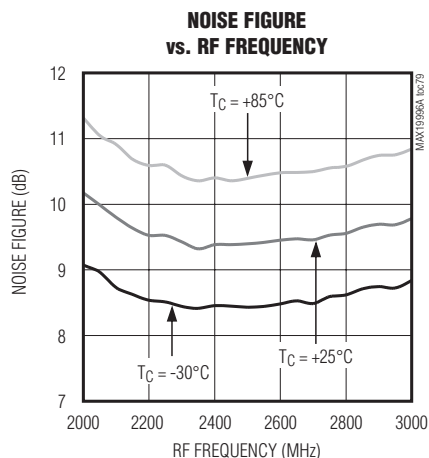
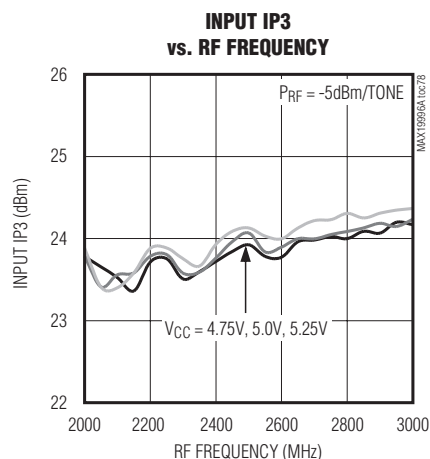
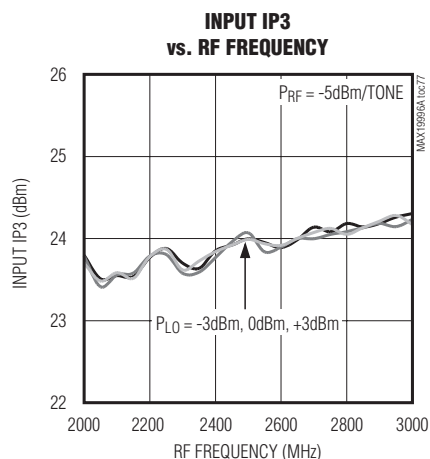
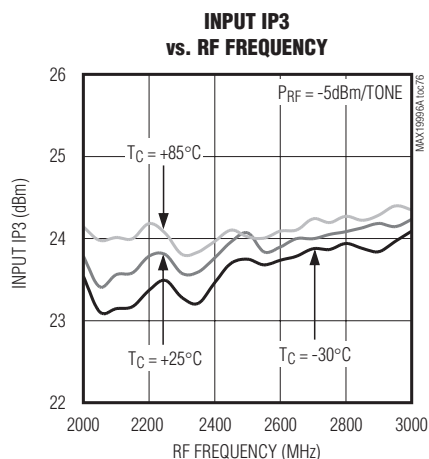
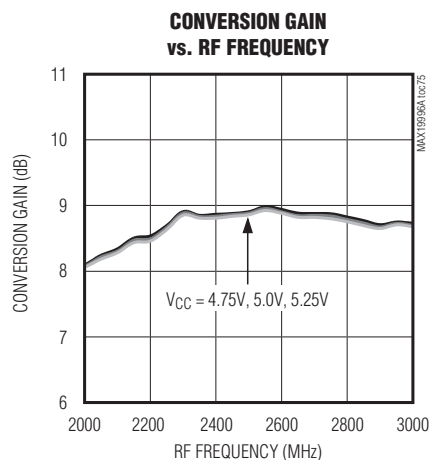
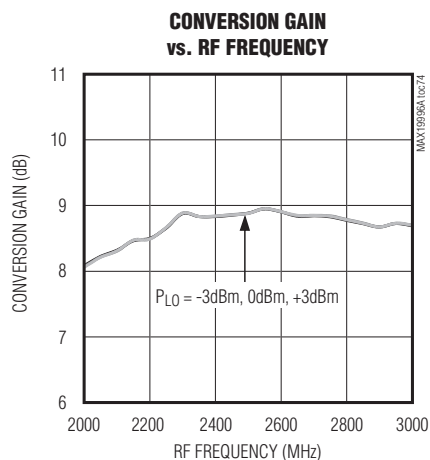
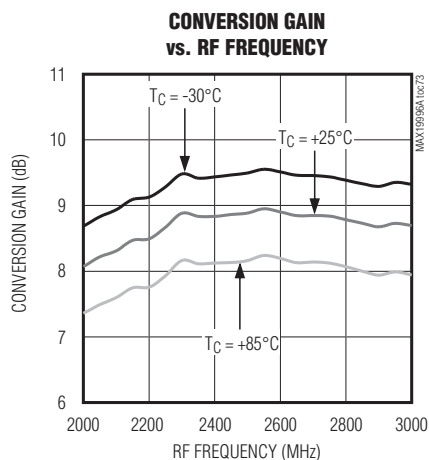
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 3.3V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

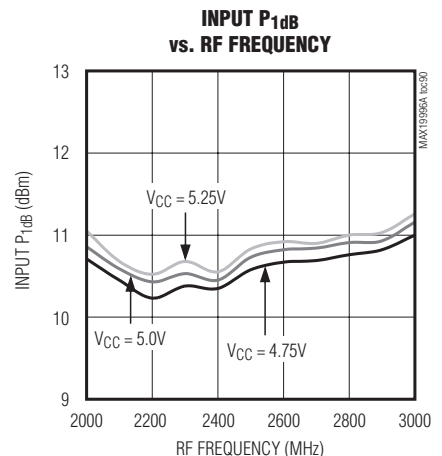
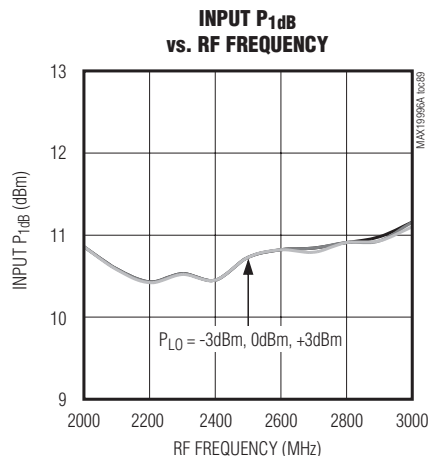
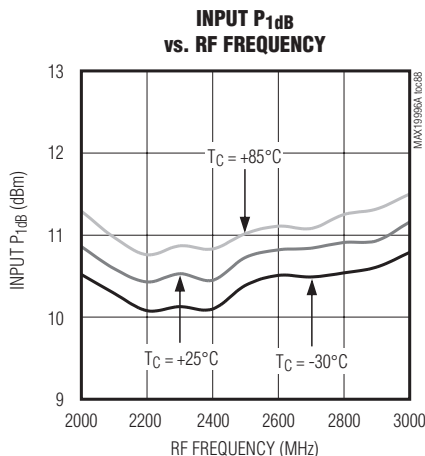
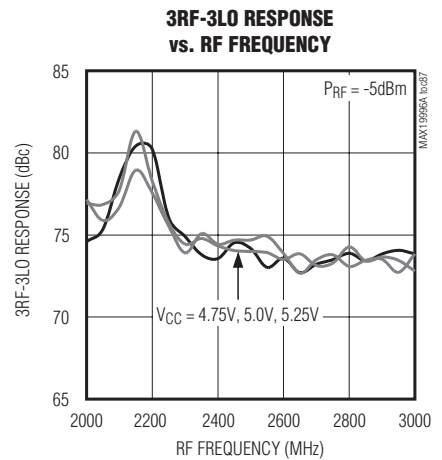
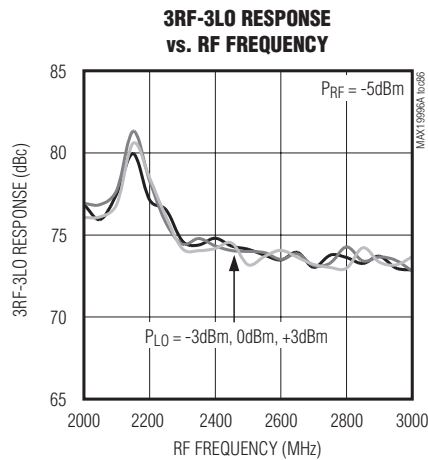
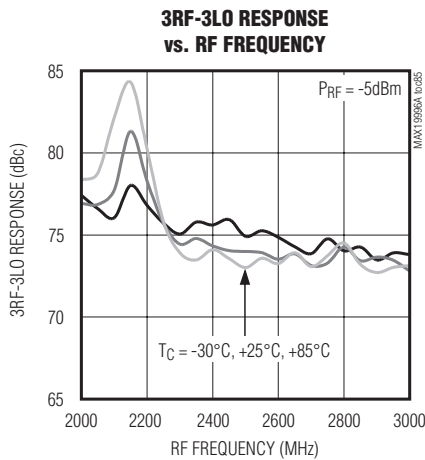
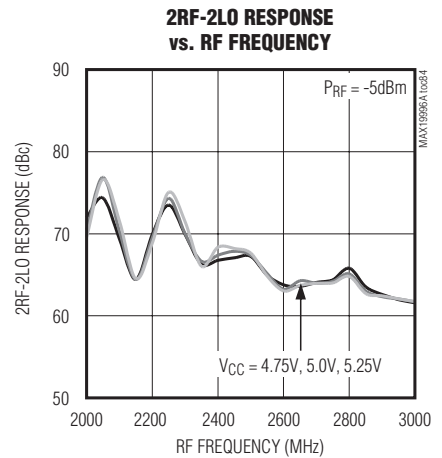
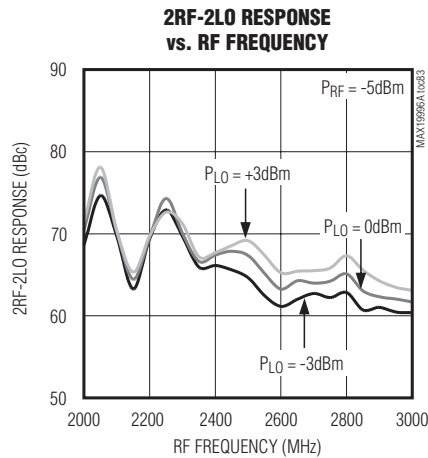
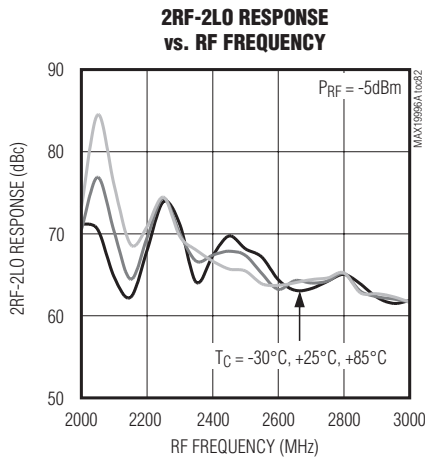


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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Typical Operating Characteristics (continued)

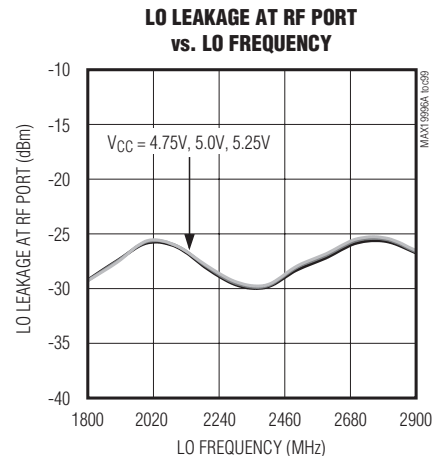
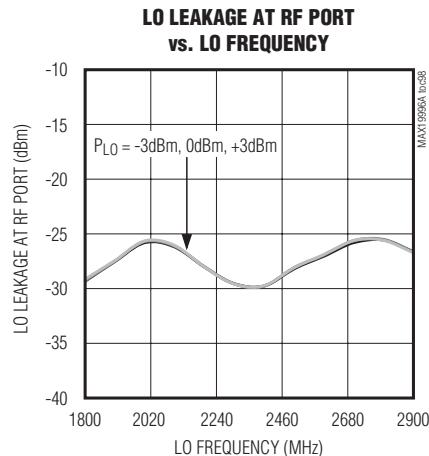
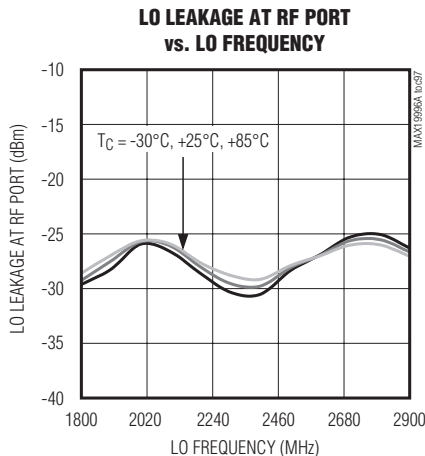
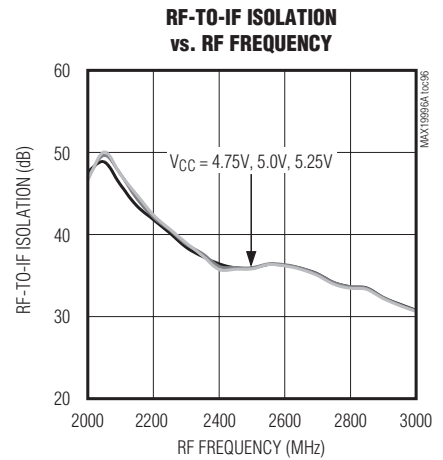
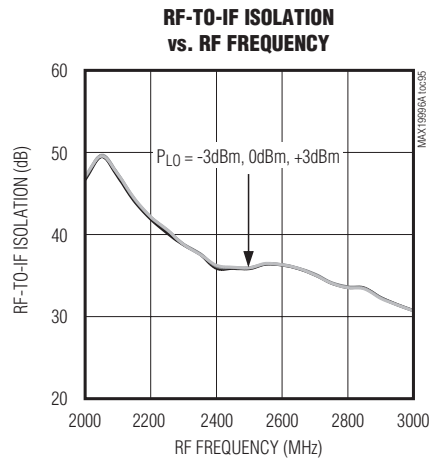
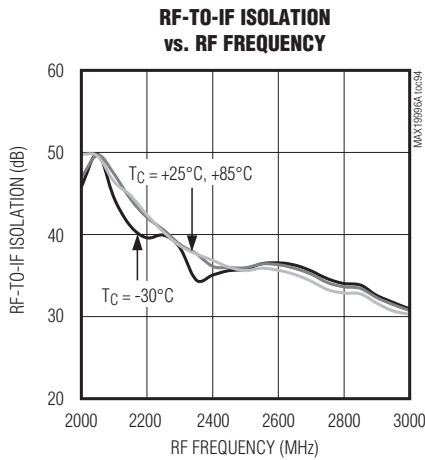
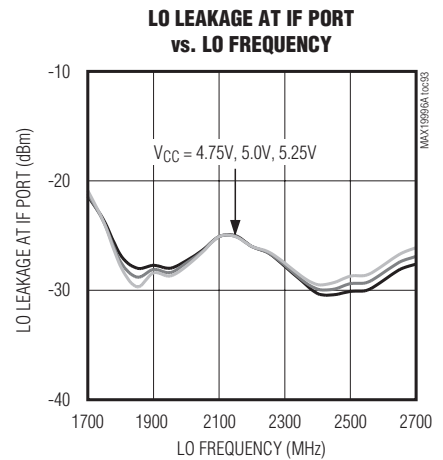
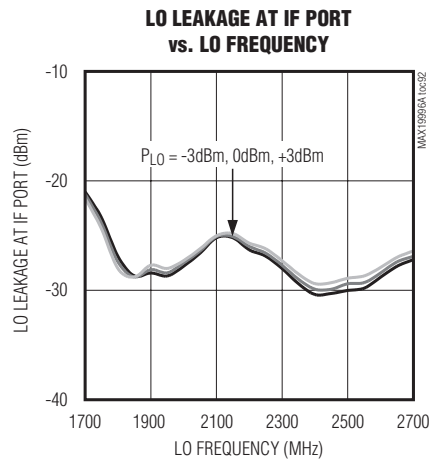
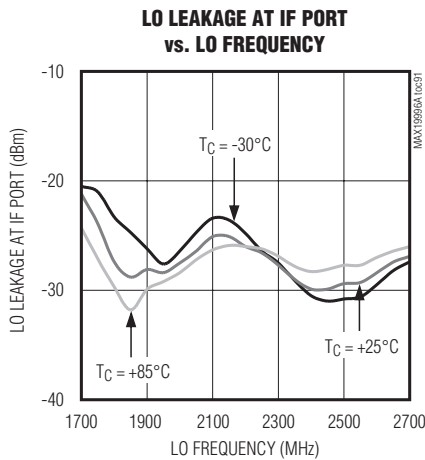
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

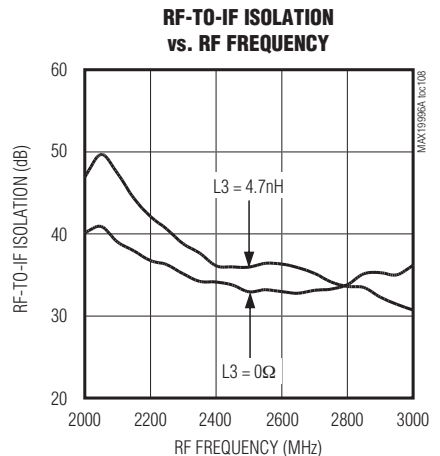
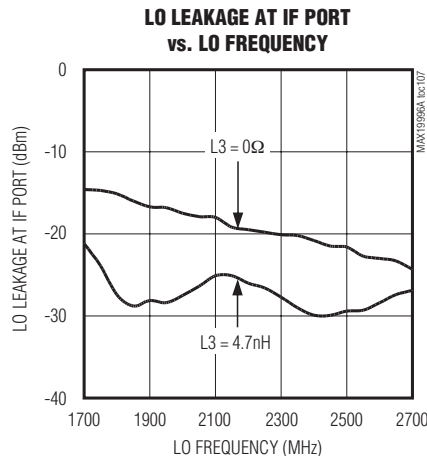
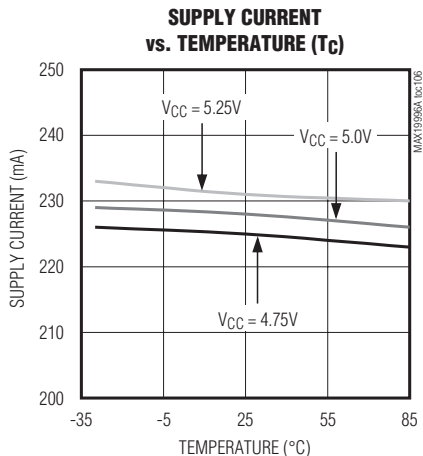
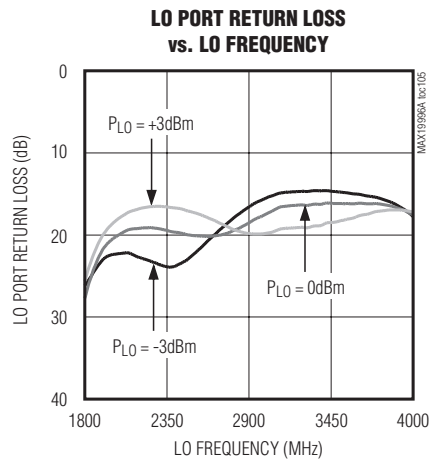
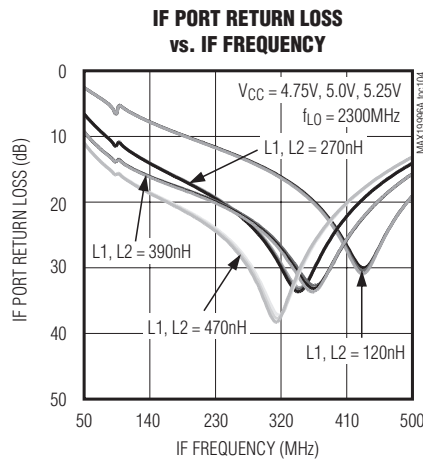
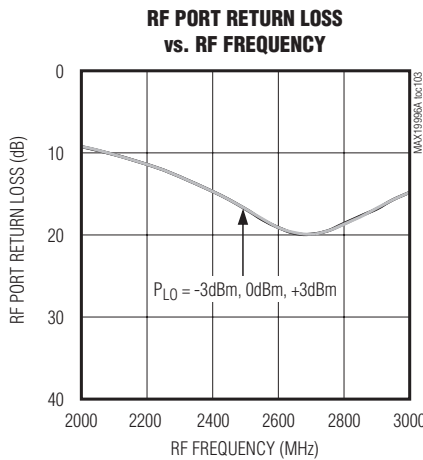
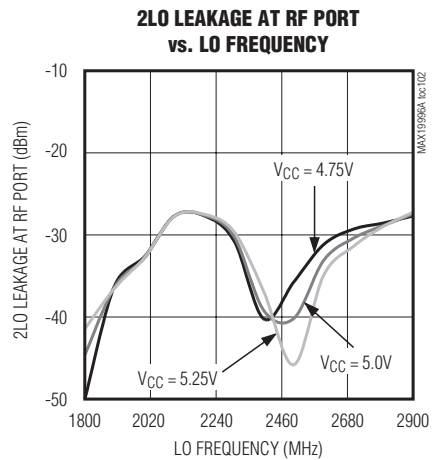
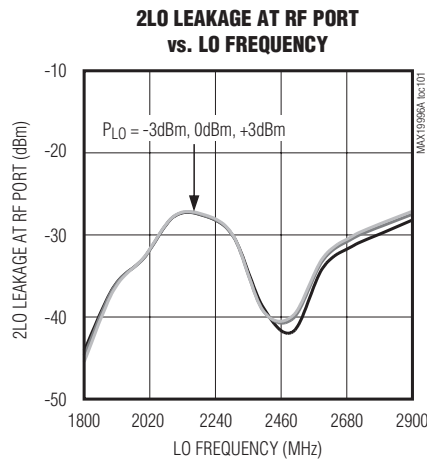
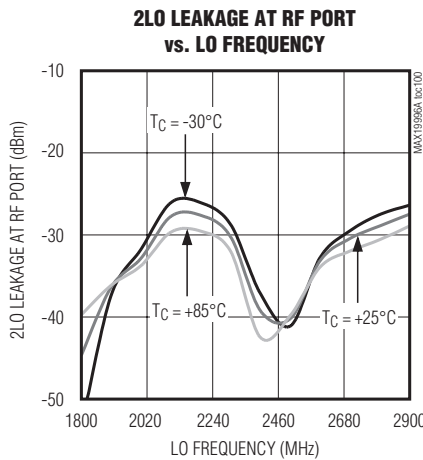


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 2000MHz$ to $3000MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

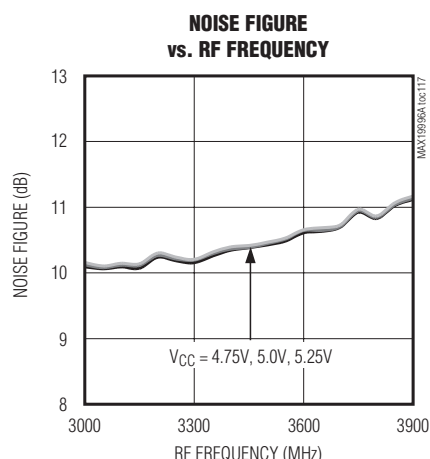
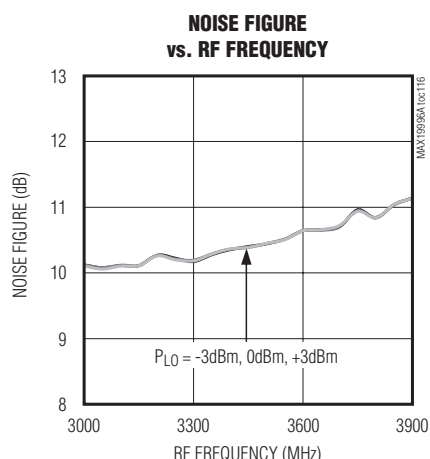
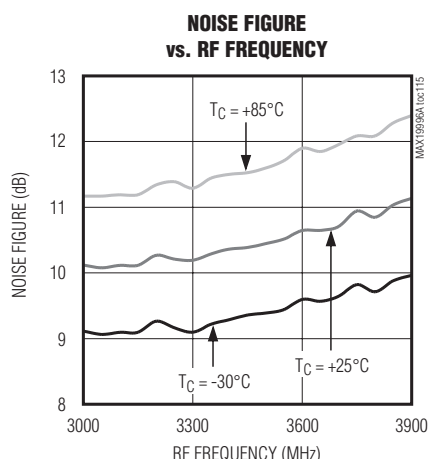
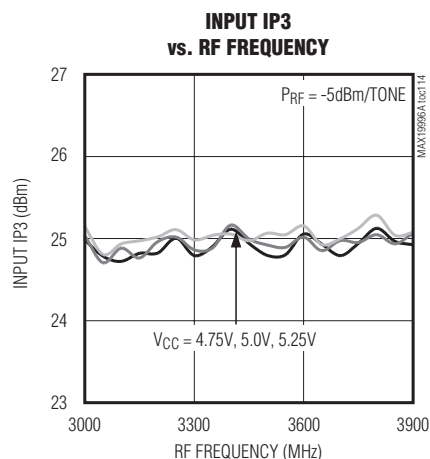
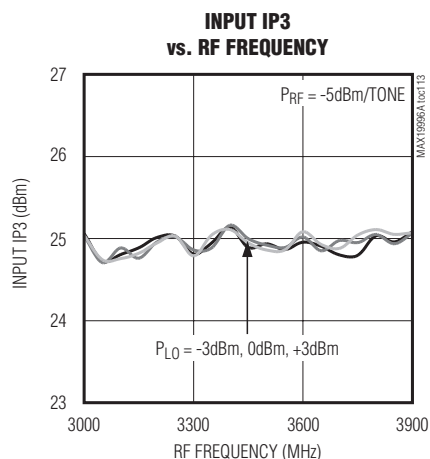
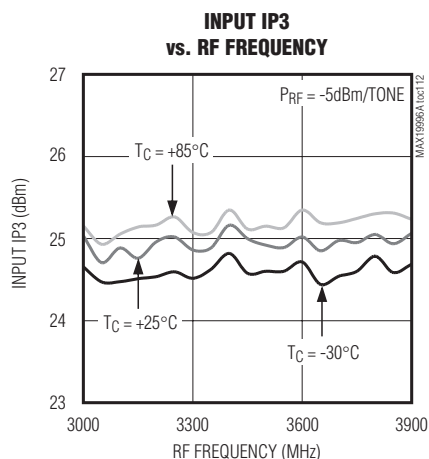
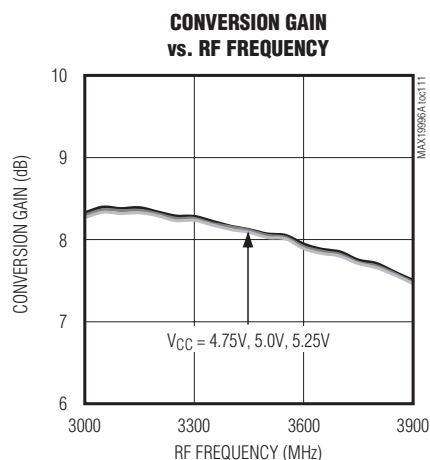
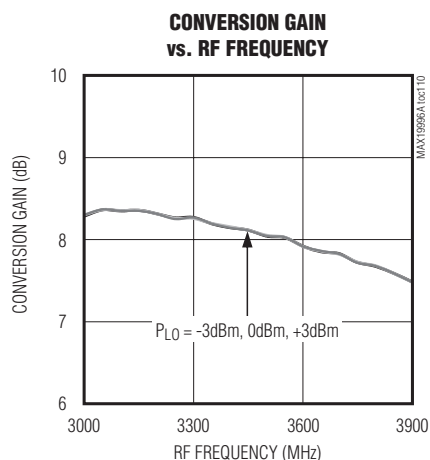
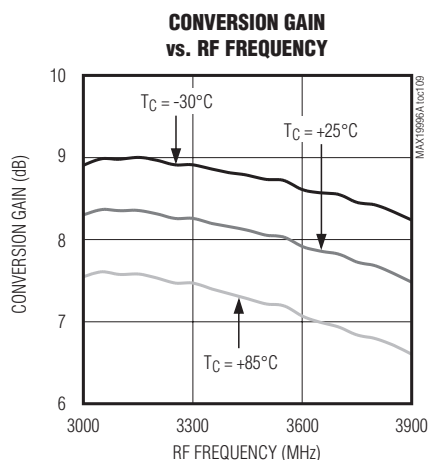
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SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3900MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

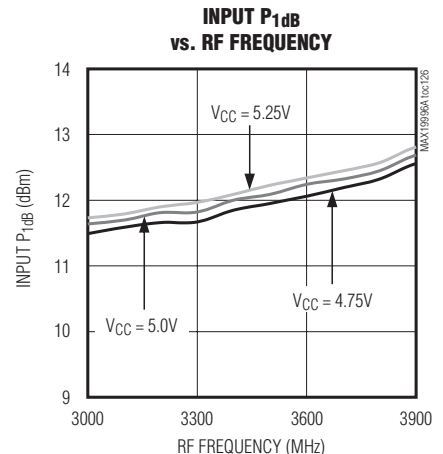
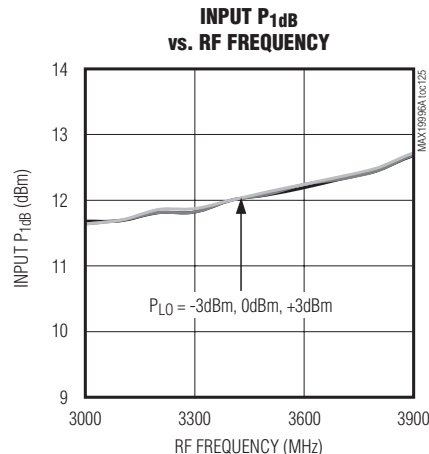
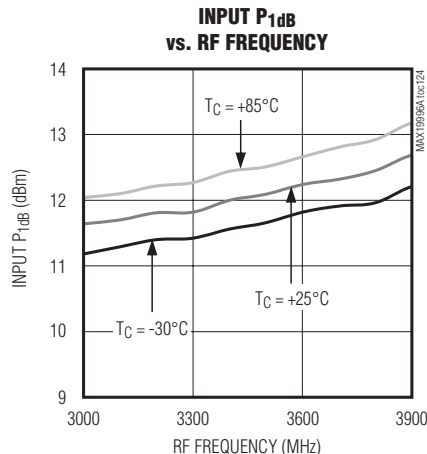
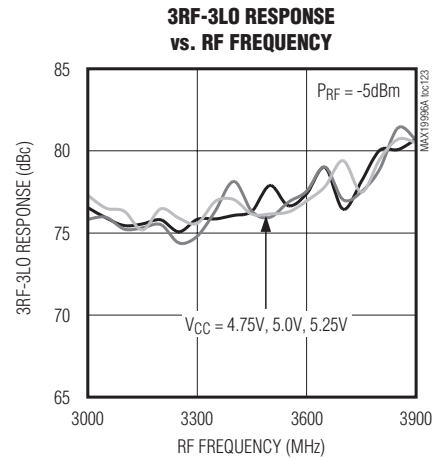
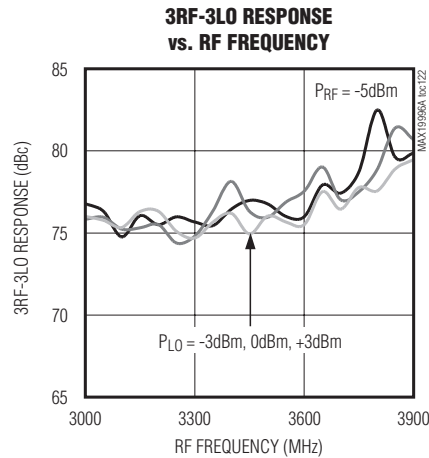
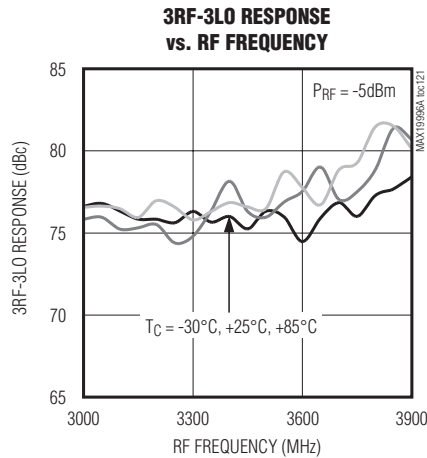
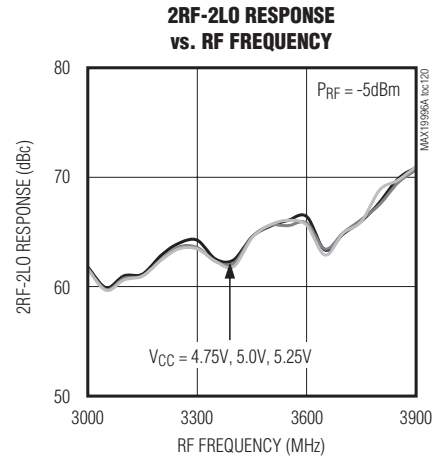
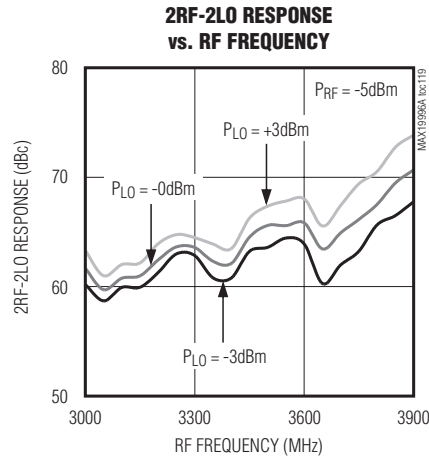
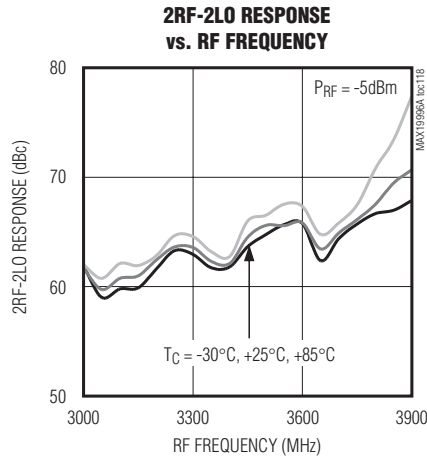


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

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Typical Operating Characteristics (continued)

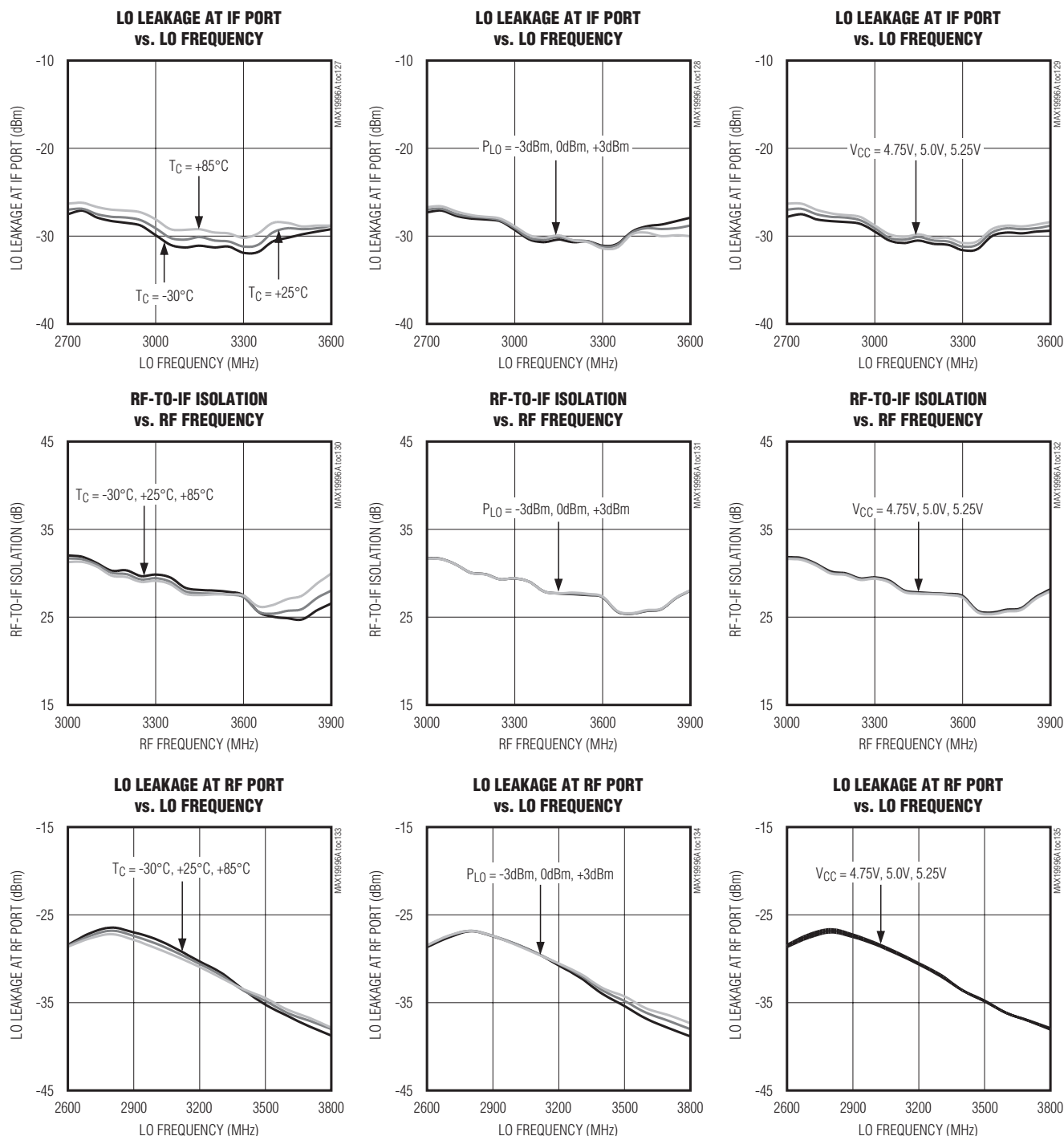
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3900MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3900MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



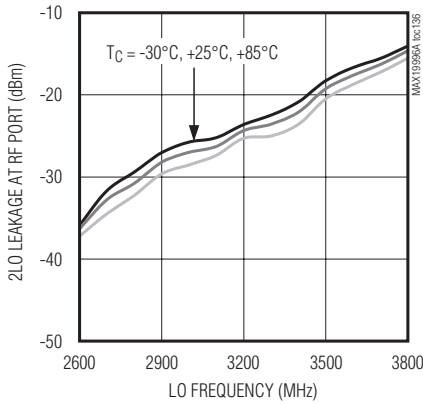
SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

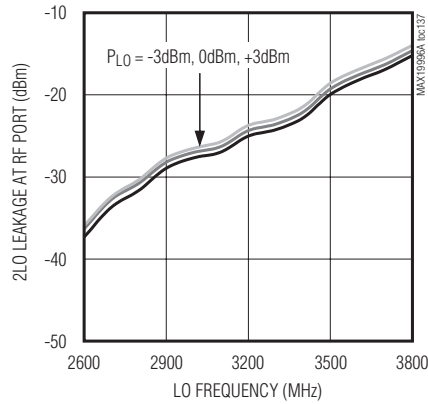
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3900MHz$, LO is low-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

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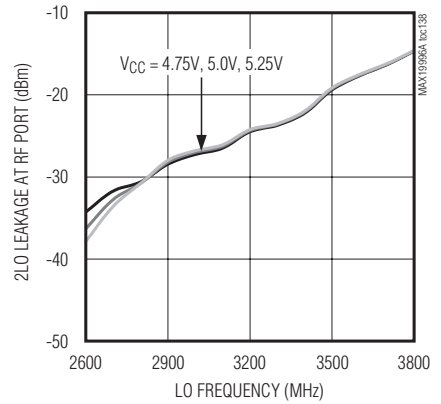
2LO LEAKAGE AT RF PORT
vs. LO FREQUENCY



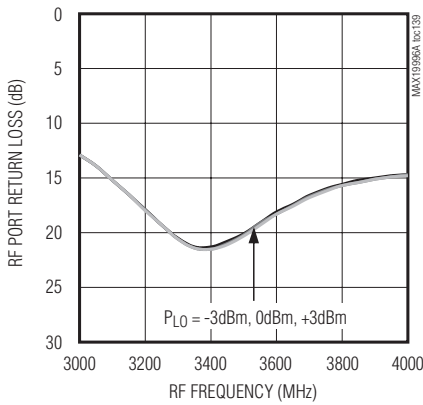
2LO LEAKAGE AT RF PORT
vs. LO FREQUENCY



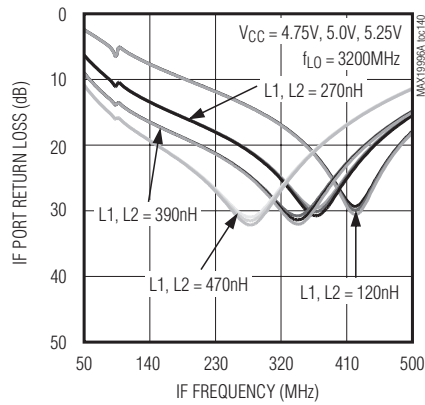
2LO LEAKAGE AT RF PORT
vs. LO FREQUENCY



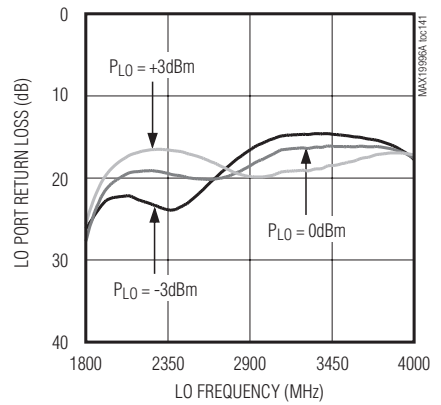
RF PORT RETURN LOSS
vs. RF FREQUENCY



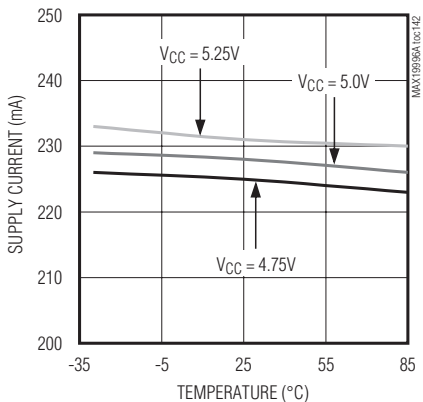
IF PORT RETURN LOSS
vs. IF FREQUENCY



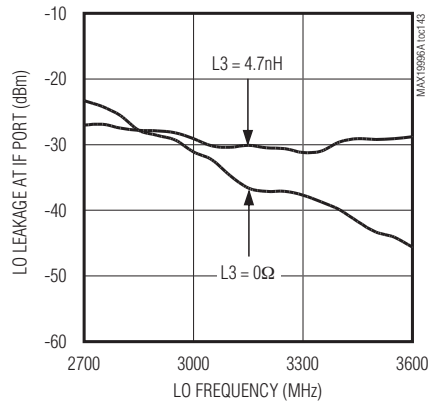
LO PORT RETURN LOSS
vs. LO FREQUENCY



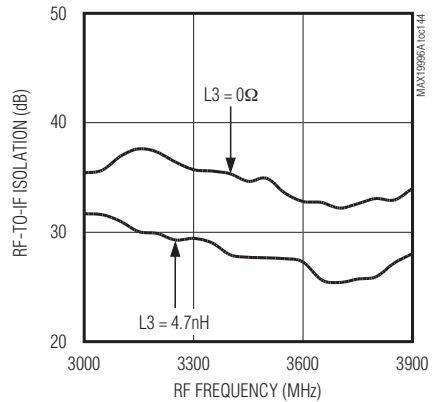
SUPPLY CURRENT
vs. TEMPERATURE (T_C)



LO LEAKAGE AT IF PORT
vs. LO FREQUENCY



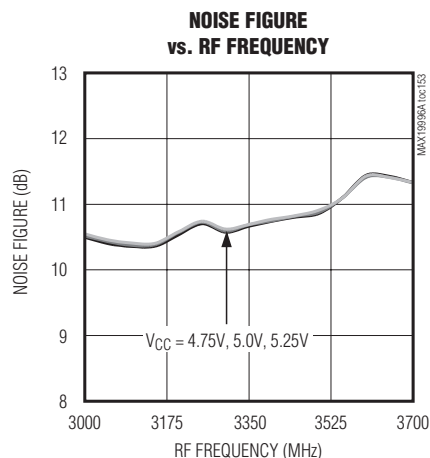
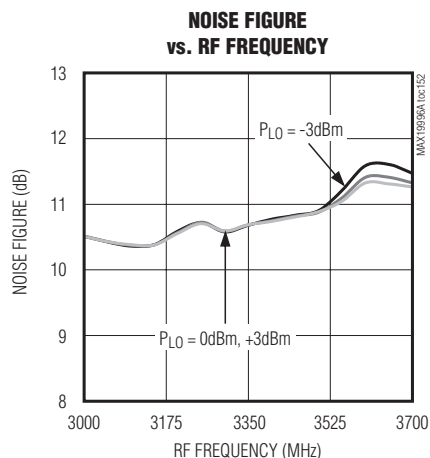
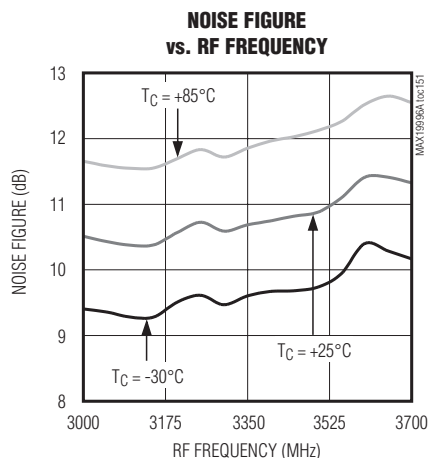
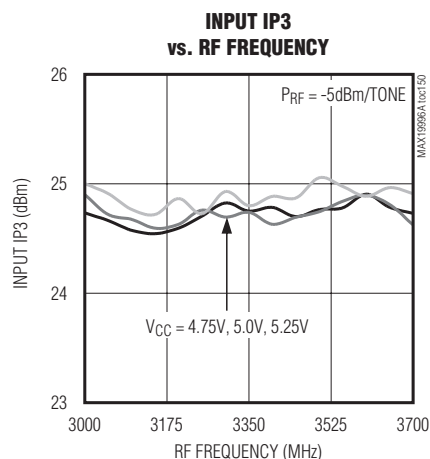
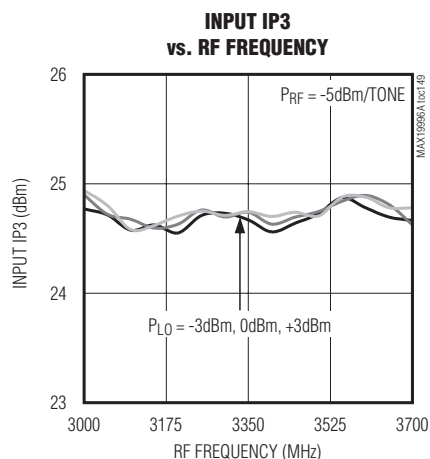
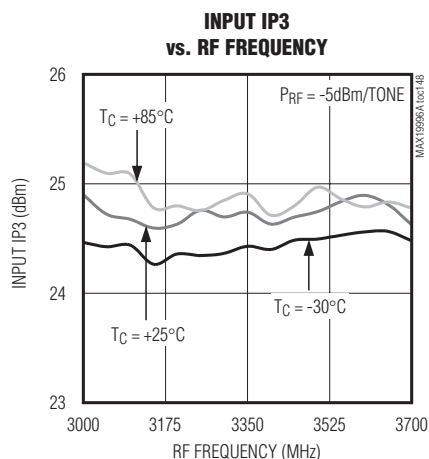
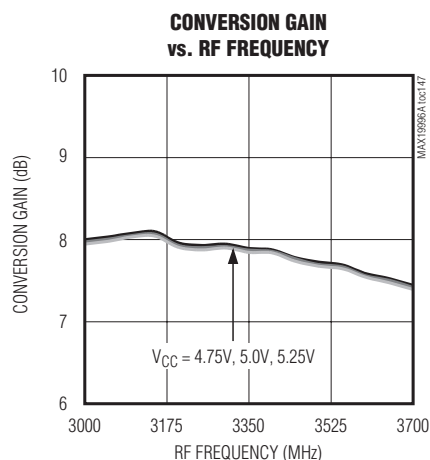
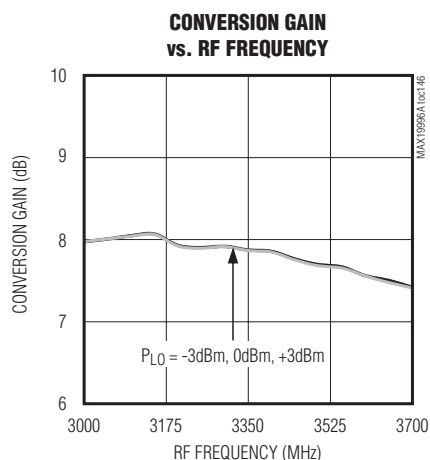
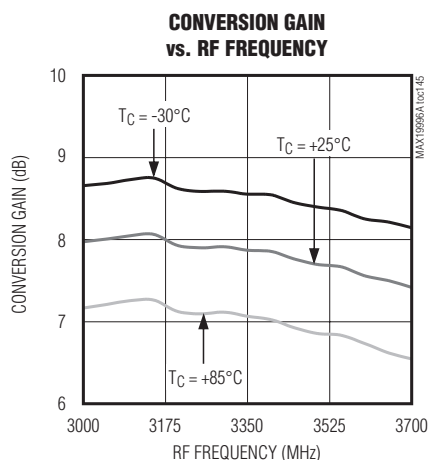
RF-TO-IF ISOLATION
vs. RF FREQUENCY



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3700MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

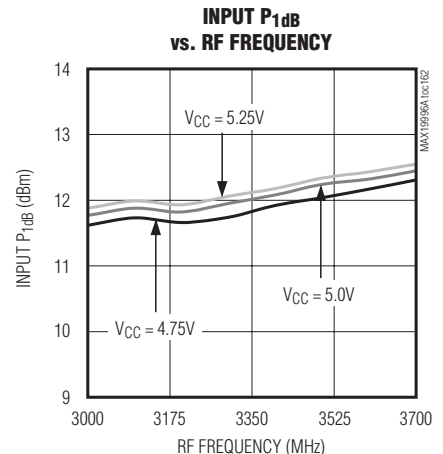
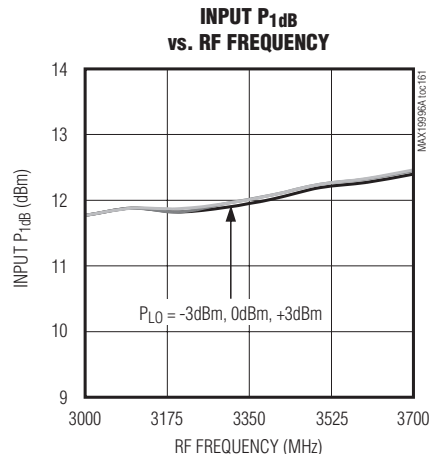
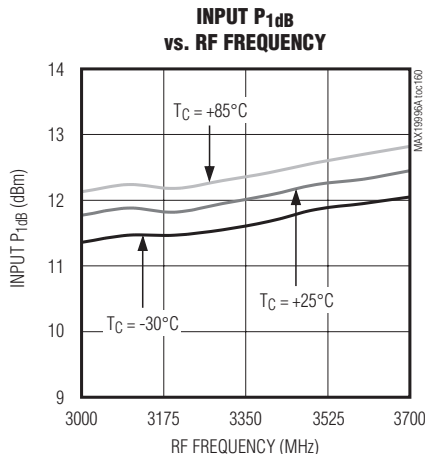
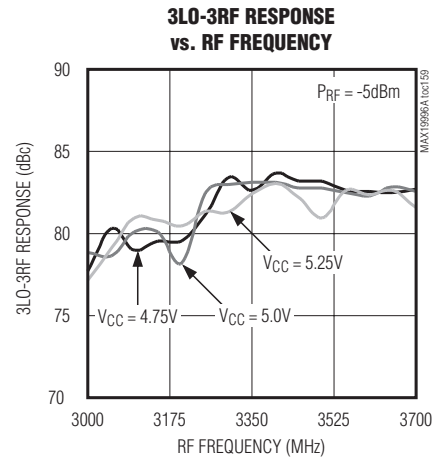
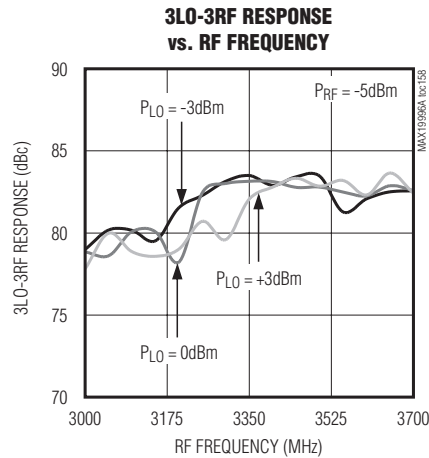
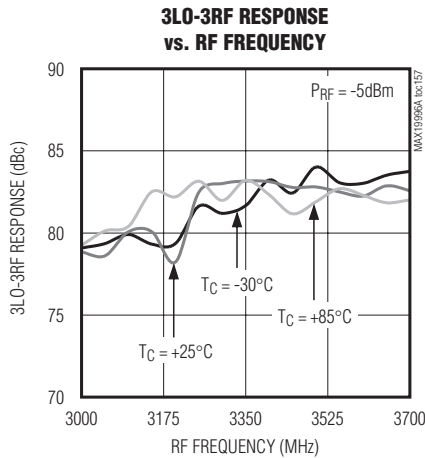
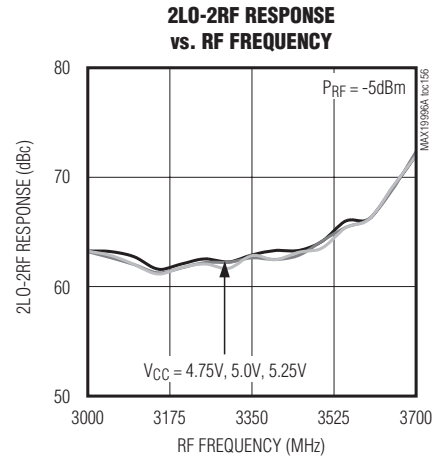
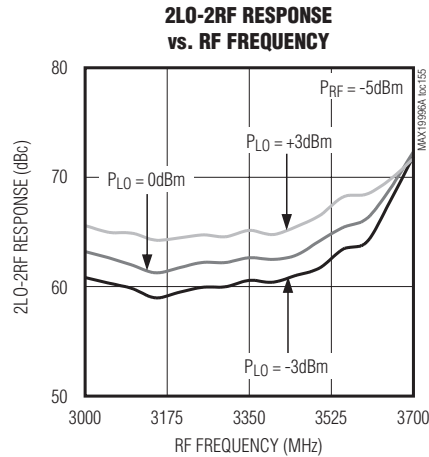
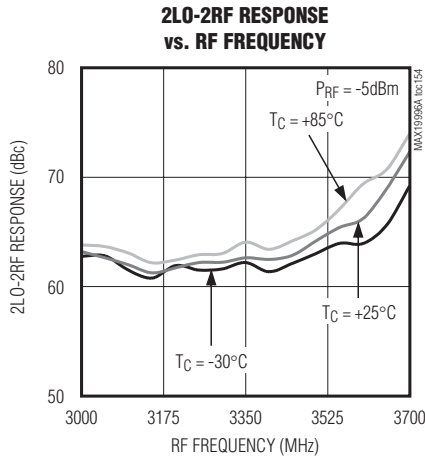


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

MAX19996A

Typical Operating Characteristics (continued)

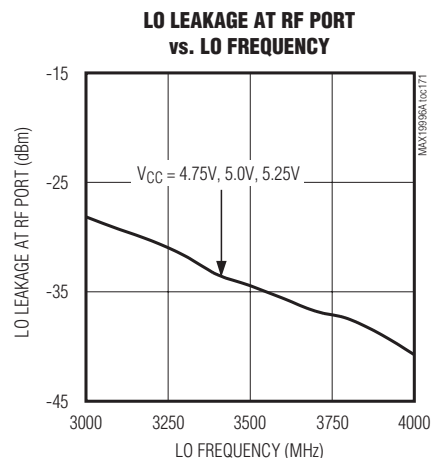
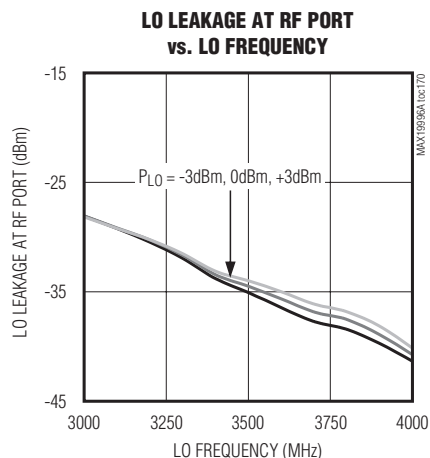
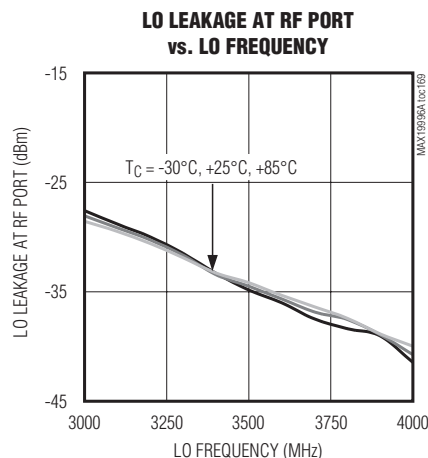
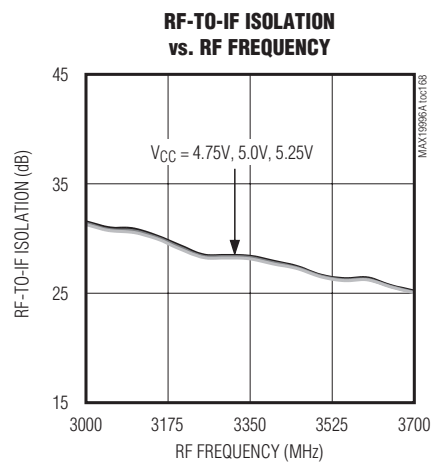
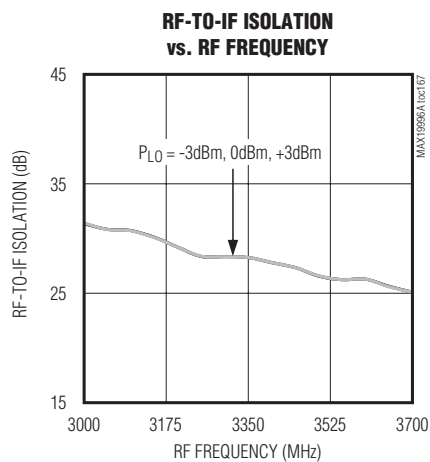
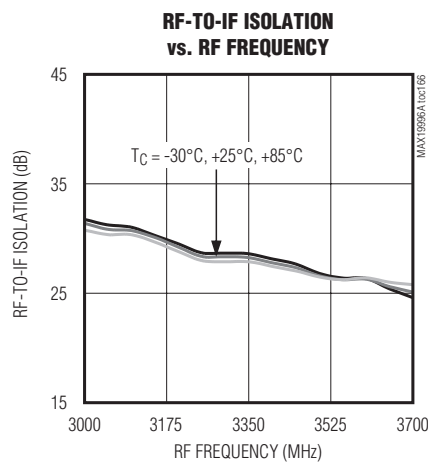
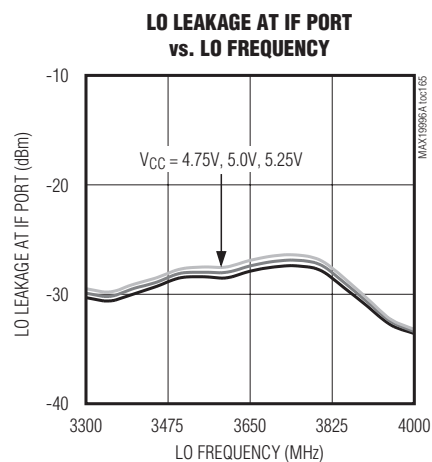
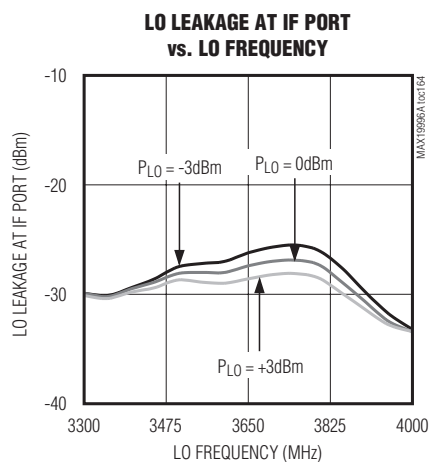
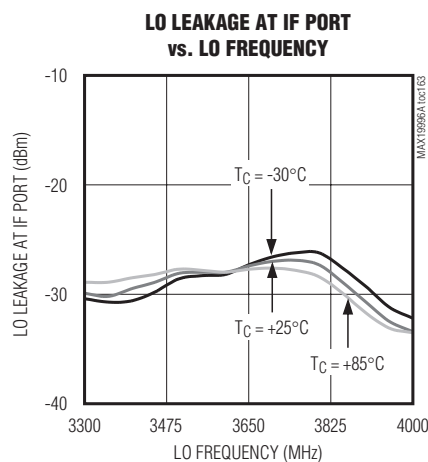
(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3700MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3700MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

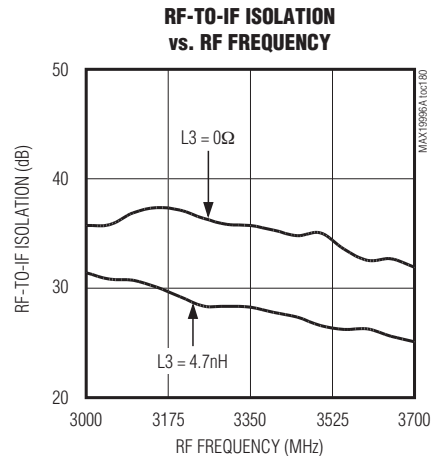
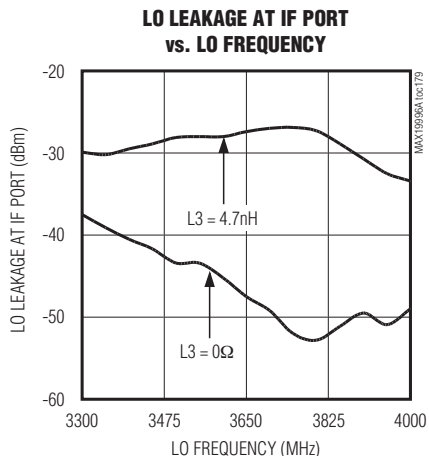
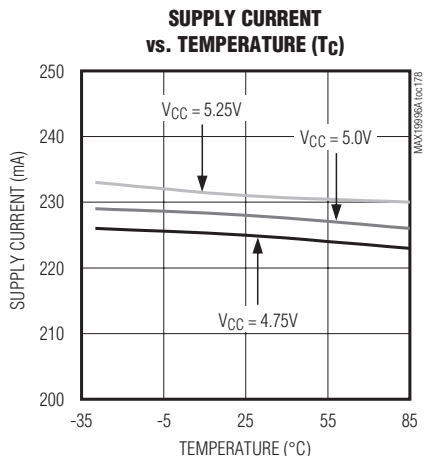
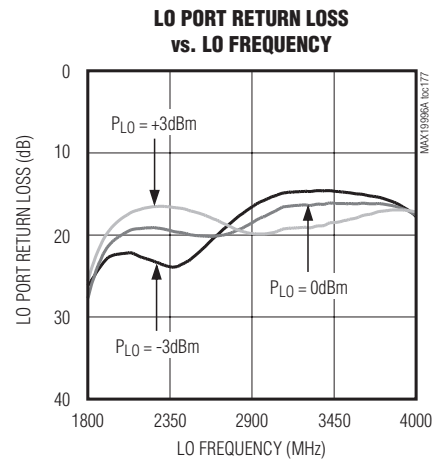
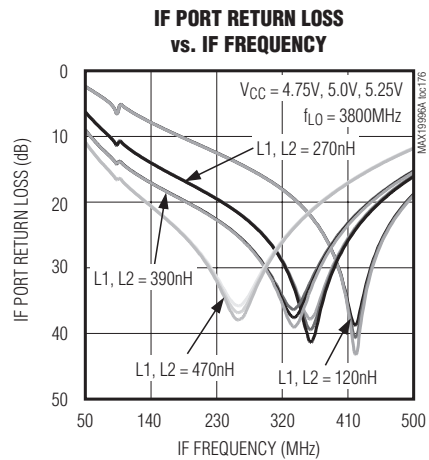
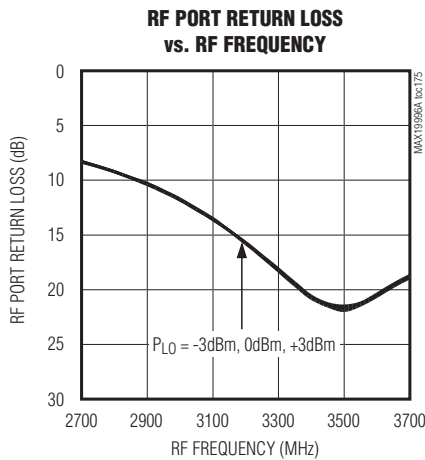
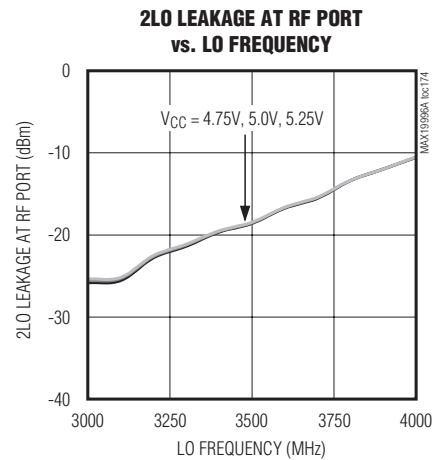
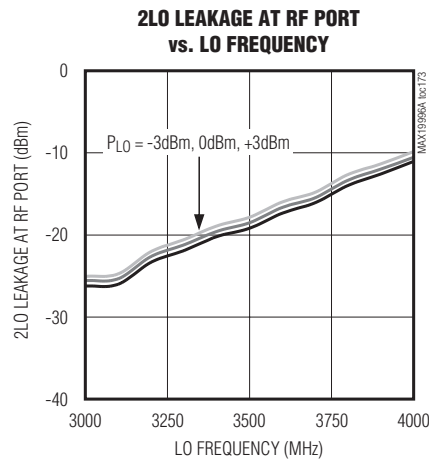
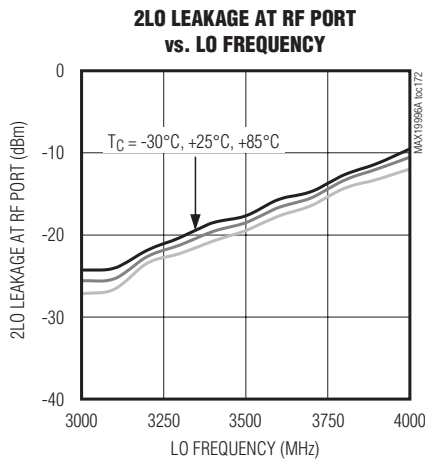


SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Typical Operating Characteristics (continued)

(Typical Application Circuit with tuning elements outlined in Table 1, $V_{CC} = 5.0V$, $f_{RF} = 3000MHz$ to $3700MHz$, LO is high-side injected for a 300MHz IF, $P_{RF} = -5dBm$, $P_{LO} = 0dBm$, $T_C = +25^\circ C$, unless otherwise noted.)

MAX19996A



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Pin Description

PIN	NAME	FUNCTION
1, 6, 8, 14	VCC	Power Supply. Bypass to GND with 0.01 μ F capacitors as close as possible to the pin.
2	RF	Single-Ended 50 Ω RF Input. Internally matched and DC shorted to GND through a balun. Requires an input DC-blocking capacitor.
3, 4, 5, 10, 12, 13, 17	GND	Ground. Internally connected to the exposed pad. Connect all ground pins and the exposed pad (EP) together.
7	LOBIAS	LO Amplifier Bias Control. Output bias resistor for the LO buffer. Connect a 604 Ω 1% (230mA bias condition) from LOBIAS to ground.
9, 15	N.C.	Not internally connected. Pins can be grounded.
11	LO	Local Oscillator Input. This input is internally matched to 50 Ω . Requires an input DC-blocking capacitor.
16	LEXT	External Inductor Connection. Connect an inductor from this pin to ground to increase the RF-to-IF and LO-to-IF isolation (see the <i>Typical Operating Characteristics</i> for typical performance vs. inductor value).
18, 19	IF-, IF+	Mixer Differential IF Output. Connect pullup inductors from each of these pins to VCC (see the <i>Typical Application Circuit</i>).
20	IFBIAS	IF Amplifier Bias Control. IF bias resistor connection for the IF amplifier. Connect a 698 Ω 1% (230mA bias condition) from IFBIAS to GND.
—	EP	Exposed Pad. Internally connected to GND. Solder this exposed pad to a PCB pad that uses multiple ground vias to provide heat transfer out of the device into the PCB ground planes. These multiple via grounds are also required to achieve the noted RF performance.

Detailed Description

When used as a high-side LO injection mixer in the 2300MHz to 2900MHz RF band, the MAX19996A provides 8.7dB of conversion gain and +24.5dBm of IIP3 with a typical noise figure of 9.8dB. The integrated baluns and matching circuitry allow for 50 Ω single-ended interfaces to the RF and the LO ports. The integrated LO buffer provides a high drive level to the mixer core, reducing the LO drive required at the MAX19996A's input to a -3dBm to +3dBm range. The IF port incorporates a differential output, which is ideal for providing enhanced 2LO-2RF performance.

Specifications are guaranteed over broad frequency ranges to allow for use in WCS, LTE, WiMAX, and MMDS base stations. The MAX19996A is specified to operate over an RF input range of 2000MHz to 3900MHz, an LO range of 2100MHz to 4000MHz, and an IF range of 50MHz to 500MHz. The external IF components set the lower frequency range (see the *Typical Operating Characteristics* for details). Operation beyond these ranges is possible (see the *Typical Operating Characteristics* for additional information).

RF Input and Balun

The MAX19996A RF input provides a 50 Ω match when combined with a series DC-blocking capacitor. This DC-blocking capacitor is required as the input is internally DC shorted to ground through the on-chip balun. When using an 8.2pF DC-blocking capacitor, the RF port input return loss is typically 14dB over the RF frequency range of 2300MHz to 2900MHz. A return loss of 15dB over the 3000MHz to 3900MHz range can be achieved by changing the DC-blocking capacitor to 1.5pF.

LO Inputs, Buffer, and Balun

With a broadband LO drive circuit spanning 2100MHz to 4000MHz, the MAX19996A can be used in either low-side or high-side LO injection architectures for virtually all 2.5GHz and 3.5GHz applications. The LO input is internally matched to 50 Ω , requiring only a 2pF DC-blocking capacitor. A two-stage internal LO buffer allows for a -3dBm to +3dBm LO input power range. The on-chip low-loss balun, along with an LO buffer, drives the double-balanced mixer. All interfacing and matching components from the LO inputs to the IF outputs are integrated on-chip.

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

High-Linearity Mixer

The core of the MAX19996A is a double-balanced, high-performance passive mixer. Exceptional linearity is provided by the large LO swing from the on-chip LO buffer. When combined with the integrated IF amplifiers, IIP3, 2LO-2RF rejection, and noise-figure performance are typically +24.5dBm, 67dBc, and 9.8dB, respectively.

Differential IF Output Amplifier

The MAX19996A has an IF frequency range of 50MHz to 500MHz, where the low-end frequency depends on the frequency response of the external IF components. The MAX19996A mixer is tuned for a 300MHz IF using 390nH external pullup bias inductors. Lower IF frequencies would require higher inductor values to maintain a good IF match. The differential, open-collector IF output ports require these inductors to be connected to VCC.

Note that these differential ports are ideal for providing enhanced 2LO-2RF and 2RF-2LO performance. Single-ended IF applications require a 4:1 (impedance ratio) balun to transform the 200 Ω differential IF impedance to a 50 Ω single-ended system. Use the TC4-1W-17 4:1 transformer for IF frequencies above 200MHz and the TC4-1W-7A 4:1 transformer for frequencies below 200MHz. The user can use a differential IF amplifier or SAW filter on the mixer IF port, but a DC block is required on both IF+/IF- ports to keep external DC from entering the IF ports of the mixer.

Applications Information

Input and Output Matching

The RF input provides a 50 Ω match when combined with a series DC-blocking capacitor. Use an 8.2pF capacitor value for RF frequencies ranging from 2000MHz to 3000MHz. A 1.5pF capacitor value should be used to match the RF port for the 3000MHz to 3900MHz band. The LO input is internally matched to 50 Ω ; use a 2pF DC-blocking capacitor to cover operations spanning the 2100MHz to 4000MHz LO range. The IF output impedance is 200 Ω (differential). For evaluation, an external low-loss 4:1 (impedance ratio) balun transforms this impedance down to a 50 Ω single-ended output (see the *Typical Application Circuit*).

Reduced-Power Mode

The MAX19996A has two pins (LOBIAS, IFBIAS) that allow external resistors to set the internal bias currents. Nominal values for these resistors are given in Table 1.

Larger value resistors can be used to reduce power dissipation at the expense of some performance loss. If $\pm 1\%$ resistors are not readily available, substitute with $\pm 5\%$ resistors.

Significant reductions in power consumption can also be realized by operating the mixer with an optional supply voltage of 3.3V. Doing so reduces the overall power consumption by up to 57%. See the 3.3V Supply AC Electrical Characteristics— $f_{RF} = 2300\text{MHz to } 2900\text{MHz}$, High-Side LO Injection table and the relevant 3.3V curves in the *Typical Operating Characteristics* section to evaluate the power vs. performance tradeoffs.

LEXT Inductor

Short LEXT to ground using a 0 Ω resistor. For applications requiring improved RF-to-IF and LO-to-IF isolation, L3 can be changed to optimize performance (see the *Typical Operating Characteristics*). However, the load impedance presented to the mixer must be so that any capacitances from IF- and IF+ to ground do not exceed several picofarads to ensure stable operating conditions. Since approximately 90mA flows through LEXT, it is important to use a low-DCR wire-wound inductor.

Layout Considerations

A properly designed PCB is an essential part of any RF/microwave circuit. Keep RF signal lines as short as possible to reduce losses, radiation, and inductance. The load impedance presented to the mixer must be so that any capacitance from both IF- and IF+ to ground does not exceed several picofarads. For the best performance, route the ground pin traces directly to the exposed pad under the package. The PCB exposed pad **MUST** be connected to the ground plane of the PCB. It is suggested that multiple vias be used to connect this pad to the lower-level ground planes. This method provides a good RF/thermal-conduction path for the device. Solder the exposed pad on the bottom of the device package to the PCB. The MAX19996A evaluation kit can be used as a reference for board layout. Gerber files are available upon request at www.maxim-ic.com.

Power-Supply Bypassing

Proper voltage-supply bypassing is essential for high-frequency circuit stability. Bypass each VCC pin with the capacitors shown in the *Typical Application Circuit* and Table 1.

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Table 1. Component Values

DESIGNATION	QTY	DESCRIPTION	COMPONENT SUPPLIER
C1	1	8.2pF microwave capacitor (0402). Use for RF frequencies ranging from 2000MHz to 3000MHz.	Murata Electronics North America, Inc.
		1.5pF microwave capacitor (0402). Use for RF frequencies ranging from 3000MHz to 3900MHz.	
C2, C6, C8, C11	4	0.01μF microwave capacitors (0402)	Murata Electronics North America, Inc.
C3, C9	0	Not installed, capacitors	—
C10	1	2pF microwave capacitor (0402)	Murata Electronics North America, Inc.
C13, C14	2	1000pF microwave capacitors (0402)	Murata Electronics North America, Inc.
C15	1	82pF microwave capacitor (0402)	Murata Electronics North America, Inc.
L1, L2	2	390nH wire-wound high-Q inductors* (0805) (see the <i>Typical Operating Characteristics</i>)	Coilcraft, Inc.
L3	1	4.7nH wire-wound high-Q inductor (0603)	Coilcraft, Inc.
R1	1	698Ω ±1% resistor (0402). Use for V_{CC} = 5.0V applications.	Digi-Key Corp.
		1.1kΩ ±1% resistor (0402). Use for V_{CC} = 3.3V applications.	
R2	1	604Ω ±1% resistor (0402). Use for V_{CC} = 5.0V applications.	Digi-Key Corp.
		845Ω ±1% resistor (0402). Use for V_{CC} = 3.3V applications.	
R3	1	0Ω resistor (1206)	Digi-Key Corp.
T1	1	4:1 IF balun TC4-1W-17*	Mini-Circuits
U1	1	MAX19996A IC (20 TQFN-EP)	Maxim Integrated Products, Inc.

*Use 470nH inductors and TC4-1W-7A 4:1 balun for IF frequencies below 200MHz.

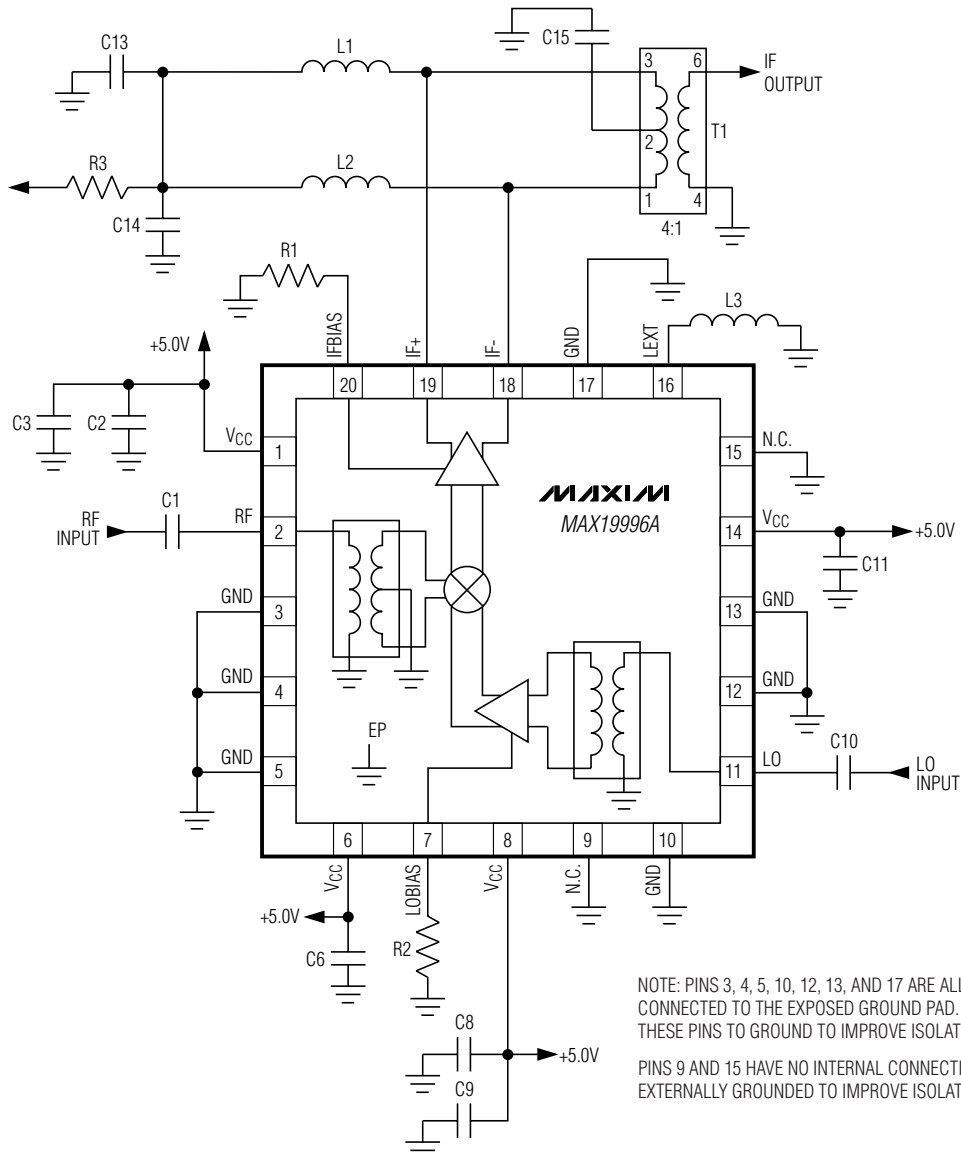
Exposed Pad RF/Thermal Considerations

The exposed pad (EP) of the MAX19996A's 20-pin thin QFN-EP package provides a low thermal-resistance path to the die. It is important that the PCB on which the MAX19996A is mounted be designed to conduct heat from the EP. In addition, provide the EP with a low-inductance path to electrical ground. The EP **MUST** be soldered to a ground plane on the PCB, either directly or through an array of plated via holes.

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

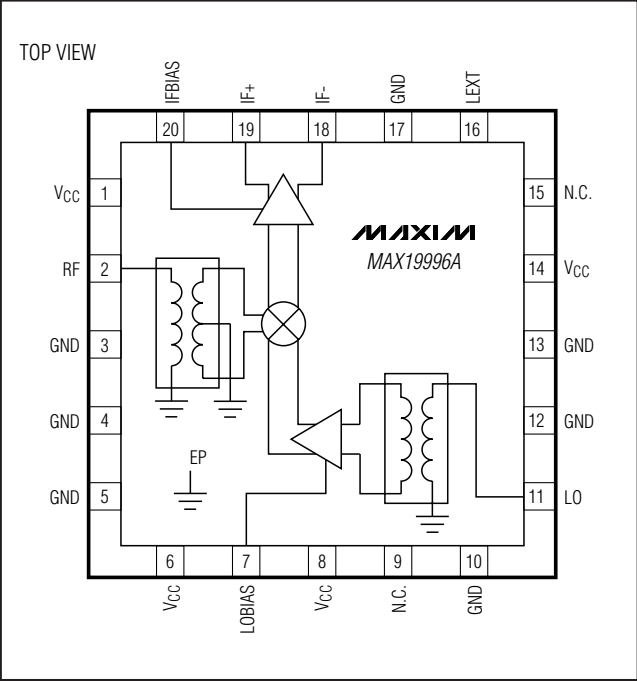
Typical Application Circuit

MAX19996A



SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Pin Configuration/ Functional Diagram



Chip Information

PROCESS: SiGe BiCMOS

Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
20 Thin QFN-EP	T2055+3	21-0140

SiGe, High-Linearity, 2000MHz to 3900MHz Downconversion Mixer with LO Buffer

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	1/09	Initial release	—
1	5/09	Updated <i>Electrical Characteristics</i> table limits	6

MAX19996A

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